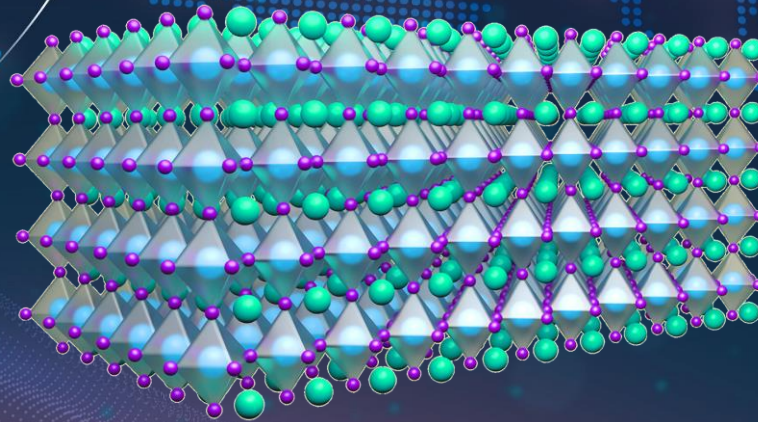


Halide Perovskite Solar Cells: Strategies for high Stability

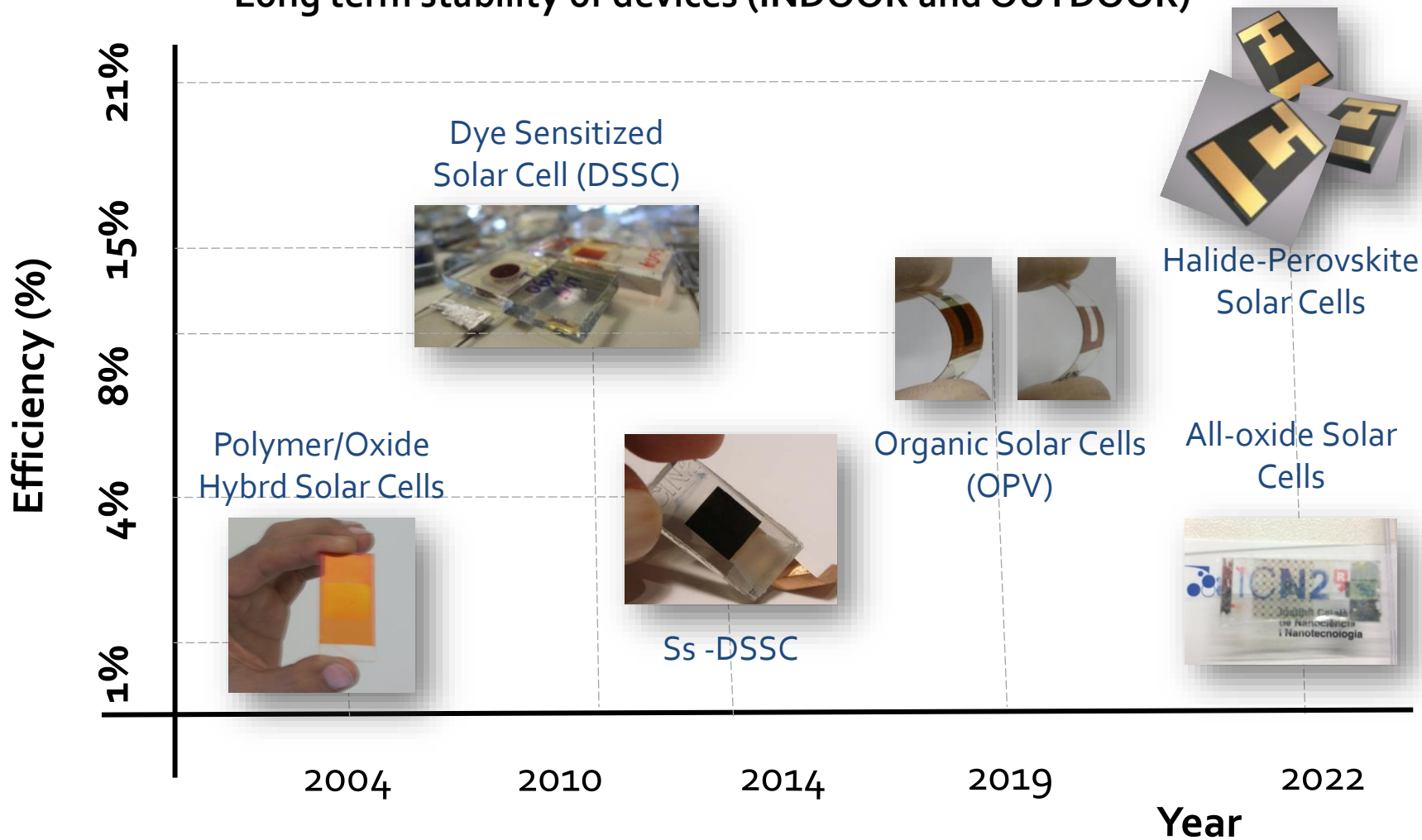
Prof. Mónica Lira-Cantu
Catalan Institute of Nanoscience and Nanotechnology (ICN2)



Ben-Gurion University of the Negev, September 5-7, 2022, Israel

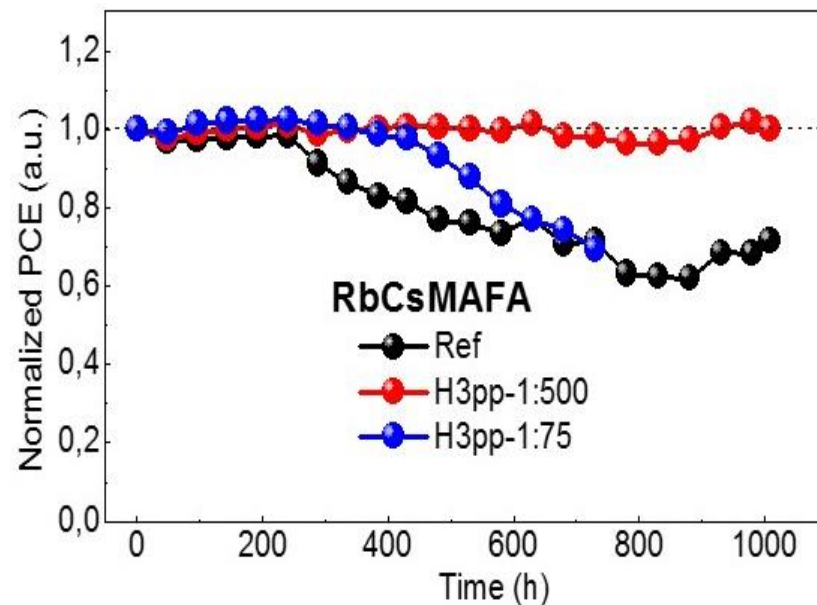
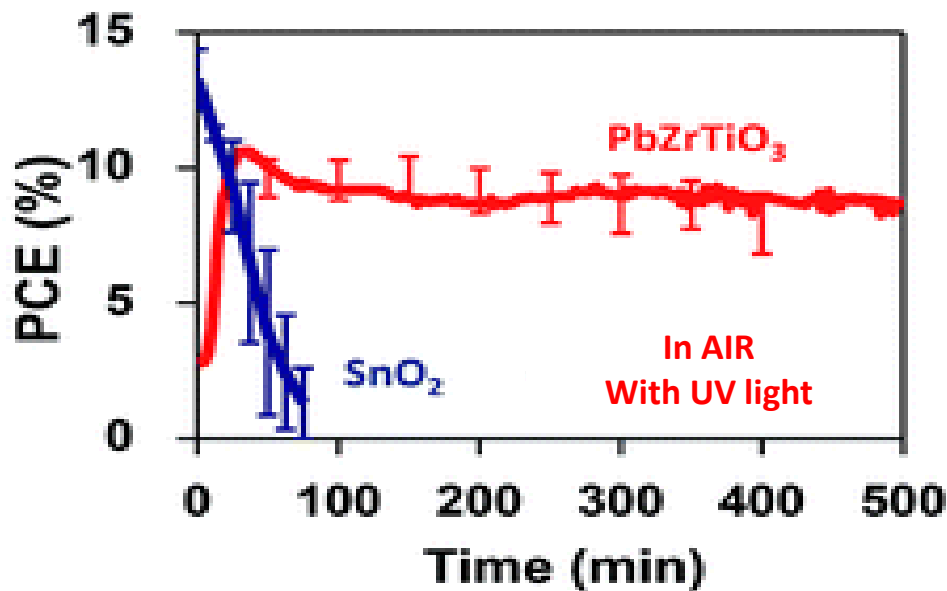
Stable EMERGING PHOTOVOLTAICS

Long term stability of devices (INDOOR and OUTDOOR)



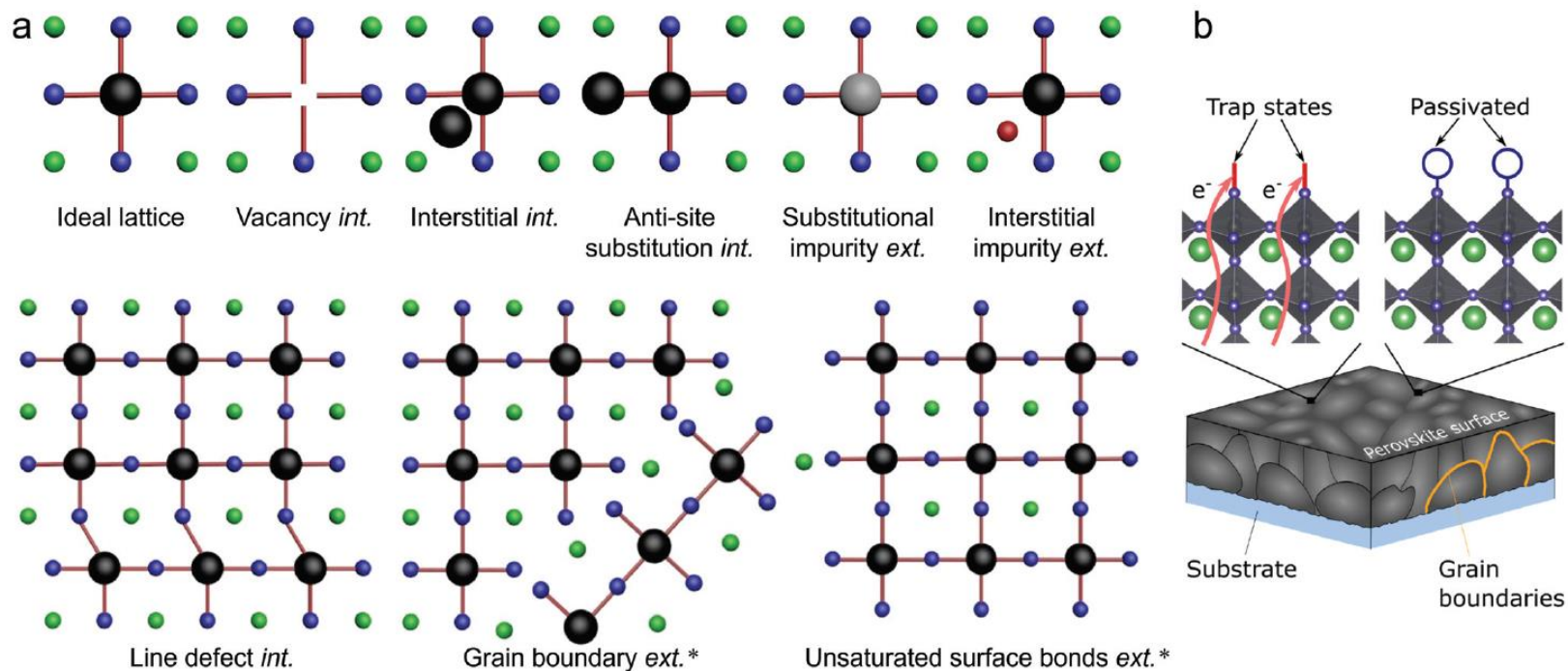
Strategies for high stability

Application of additives



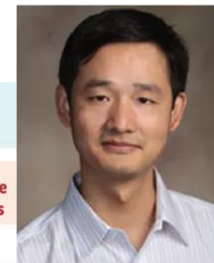
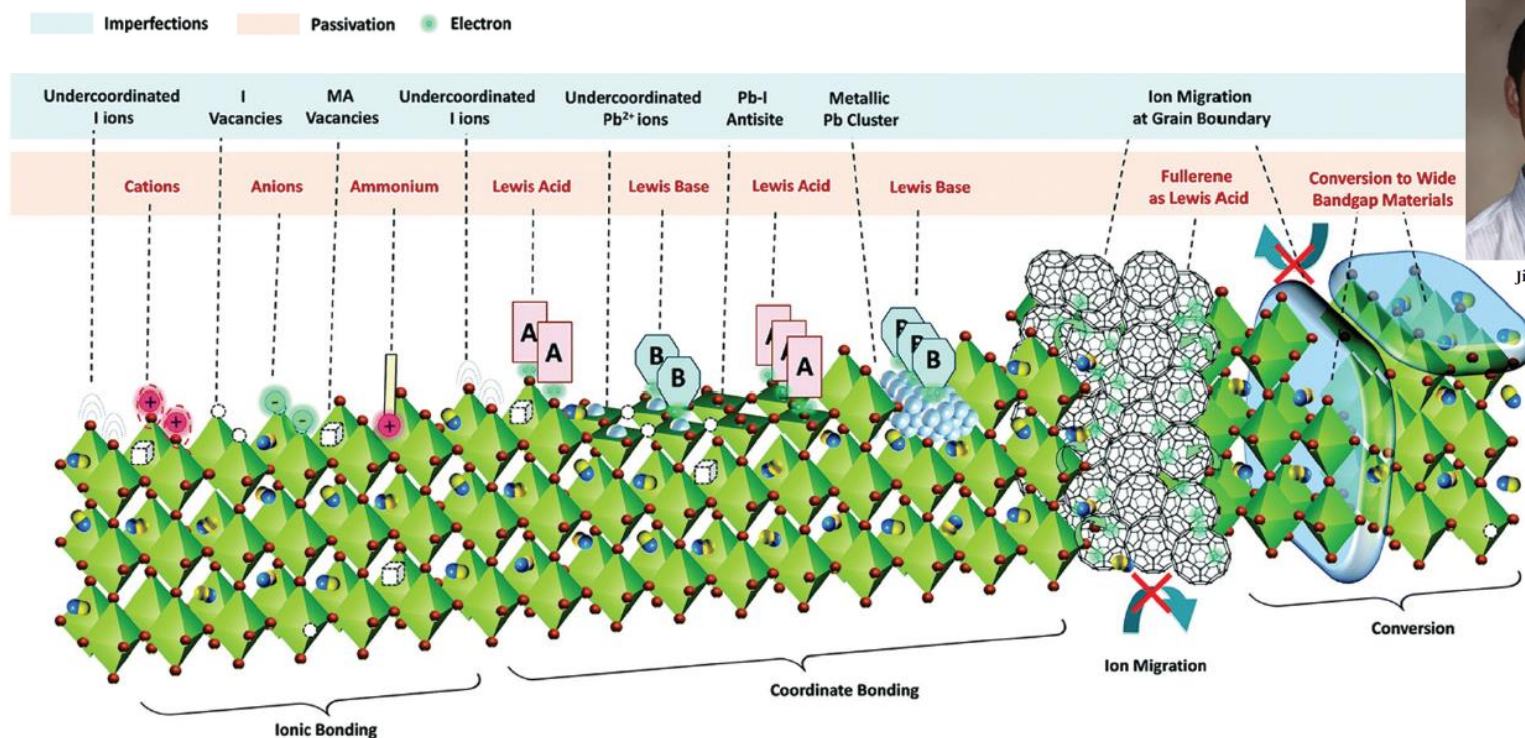
Use of Ferroelectric Oxides

Defects in Halide Perovskites



Defects are recombination centers and induce device degradation under non-equilibrium conditions.

Defect passivation and suppressing ion migration



Jinsong Huang

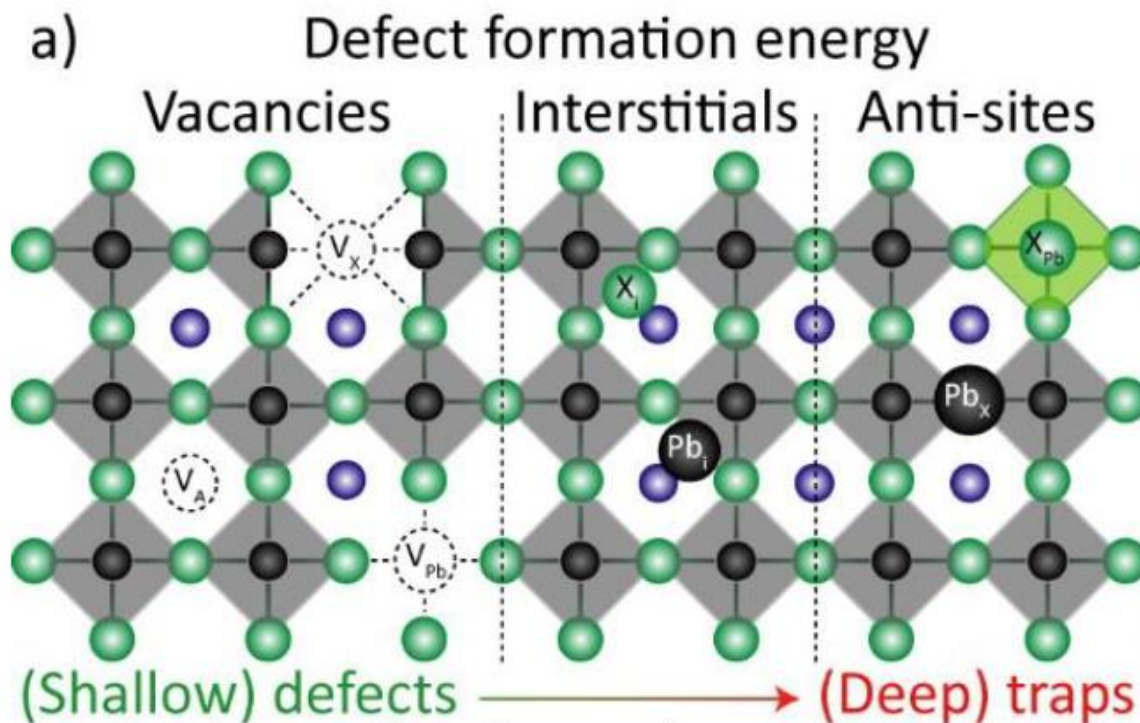
Defects

- Deep level traps → Major non-radiative recombination centers (affect Voc and Efficiency)
- Shallow level charge traps → Ion migration

Defect Formation

ionic-electronic properties

non-radiative recombination



Increasing formation energy (or decreasing probability of occurrence)

Point defects

Deep level traps:

- undercoordinated halides ions
- undercoordinated Pb_{2+} ions,
- lead clusters
- Pb–I antisite defects (PbI_3) – from process fabrication

Shallow level traps:

- I or MA vacancies in the bulk of the material

Example: 12 Point defects in the methylammonium lead triiodide (MAPbI_3):

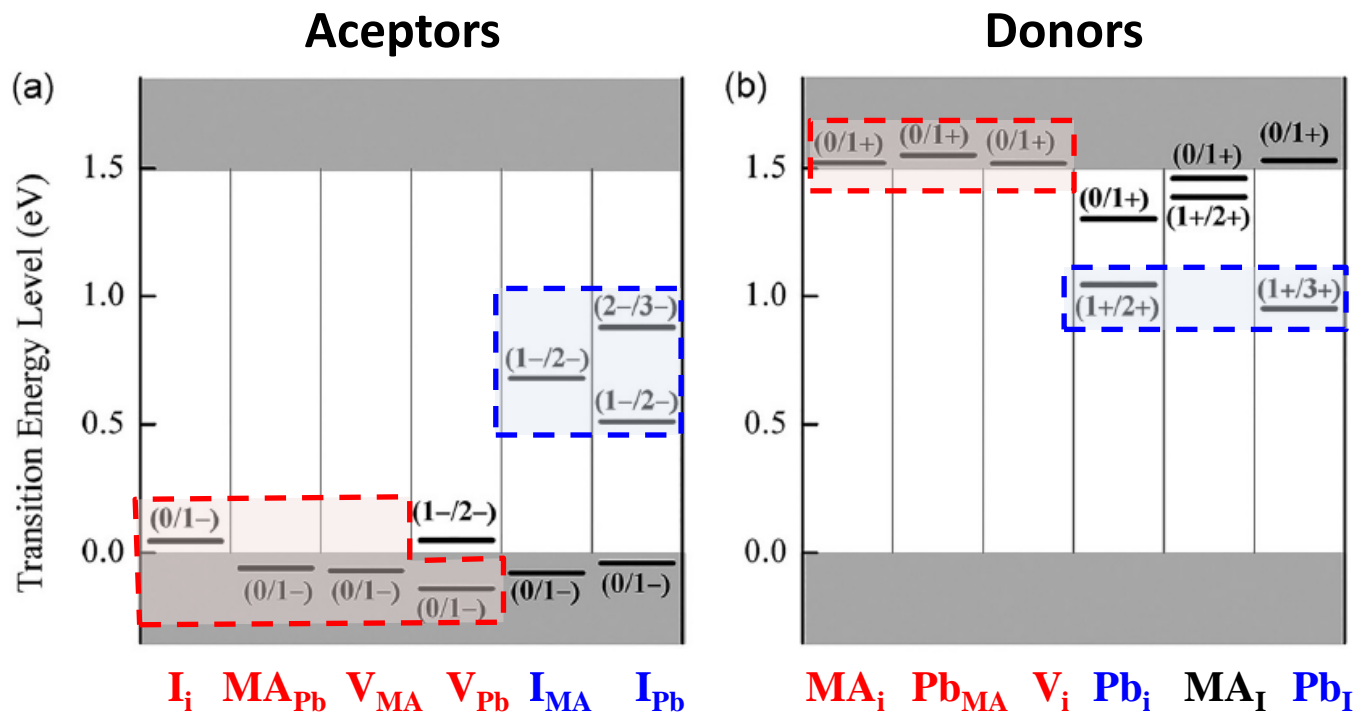
Three types of vacancies (V_{MA} , V_{Pb} , V_{I})

Three types of interstitial sites (MA_i , Pb_i , I_i)

Two types of cation substitutions (MA_{Pb} , Pb_{MA})

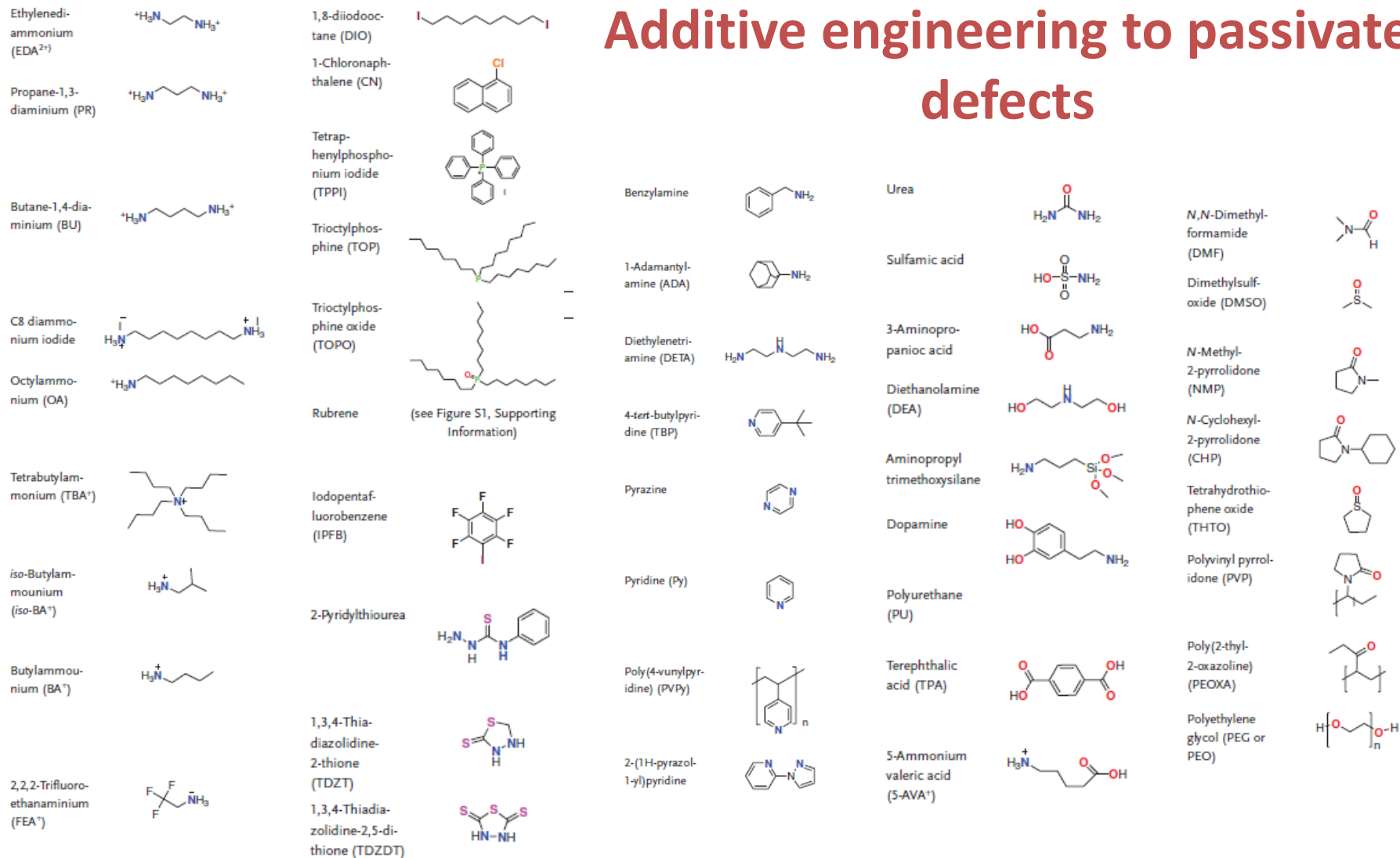
Four types of antisite substitutions (MA_i , Pb_i , I_{MA} , I_{Pb})

Point defects



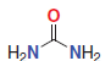
Shallow Point Defects - Low formation Energy
Deep Point Defects - High formation Energy

Additive engineering to passivate defects

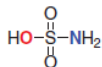


Additive engineering in PSC

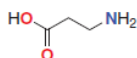
Urea



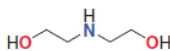
Sulfamic acid



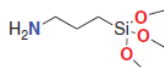
3-Aminopropionic acid



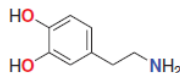
Diethanolamine (DEA)



Aminopropyl trimethoxysilane

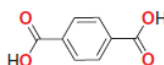


Dopamine

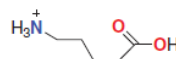


Polyurethane (PU)

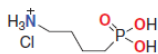
Terephthalic acid (TPA)



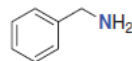
5-Ammonium valeric acid (5-AVA⁺)



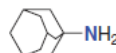
4-phosphobutan-1-aminium



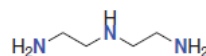
Benzylamine



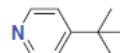
1-Adamantylamine (ADA)



Diethylenetriamine (DETA)



4-*tert*-butylpyridine (TBP)



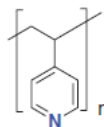
Pyrazine



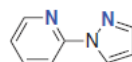
Pyridine (Py)



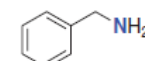
Poly(4-vinylpyridine) (PVPy)



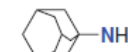
2-(1H-pyrazol-1-yl)pyridine



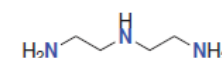
Benzylamine



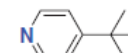
1-Adamantylamine (ADA)



Diethylenetriamine (DETA)



4-*tert*-butylpyridine (TBP)



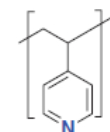
Pyrazine



Pyridine (Py)

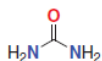


Poly(4-vinylpyridine) (PVPy)

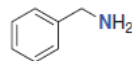


Additive engineering in PSC

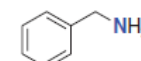
Urea



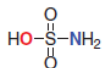
Benzylamine



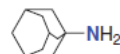
Benzylamine



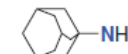
Sulfamic acid



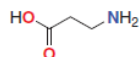
1-Adamantylamine (ADA)



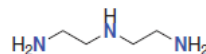
1-Adamantylamine (ADA)



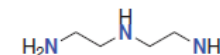
3-Aminopropionic acid



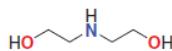
Diethylenetriamine (DETA)



Diethylenetriamine (DETA)



Diethanolamine (DEA)



How to select the best additive to enhance efficiency and stability???

Dopamine



Imine (IBP)



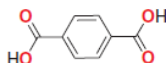
Polyurethane (PU)



Pyrazine



Terephthalic acid (TPA)



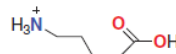
Pyridine (Py)



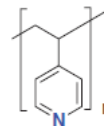
Pyridine (Py)



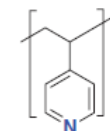
5-Ammonium valeric acid (5-AVA⁺)



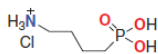
Poly(4-vinylpyridine) (PVPy)



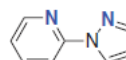
Poly(4-vinylpyridine) (PVPy)



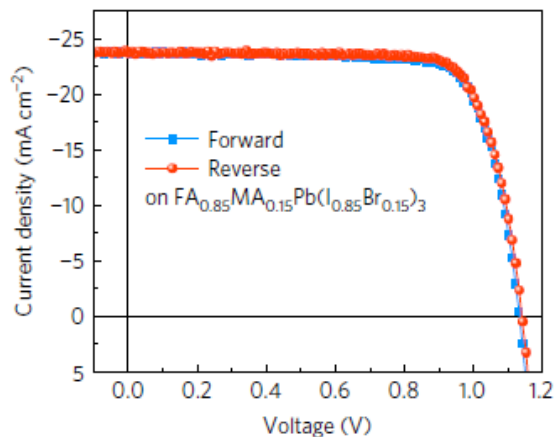
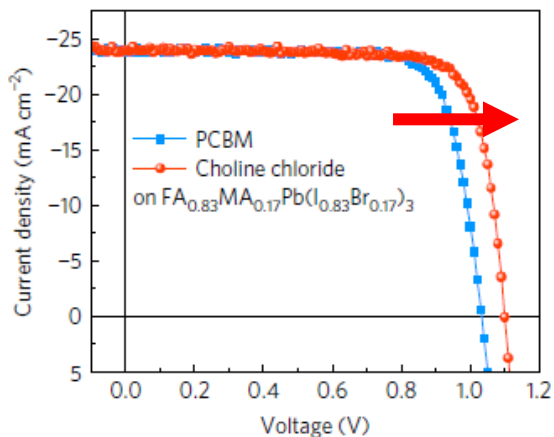
4-phosphobutan-1-aminium



2-(1H-pyrazol-1-yl)pyridine

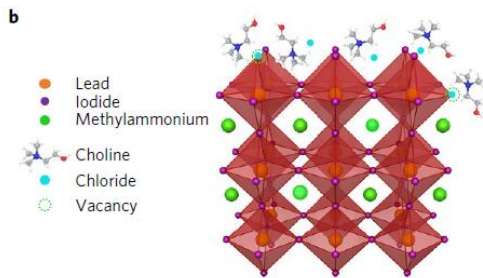
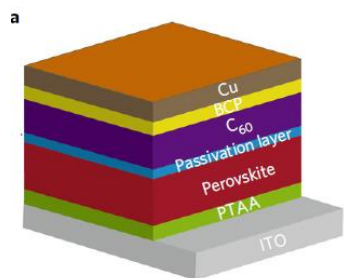


Passivation with zwitterions (positively and negatively charged functional groups)

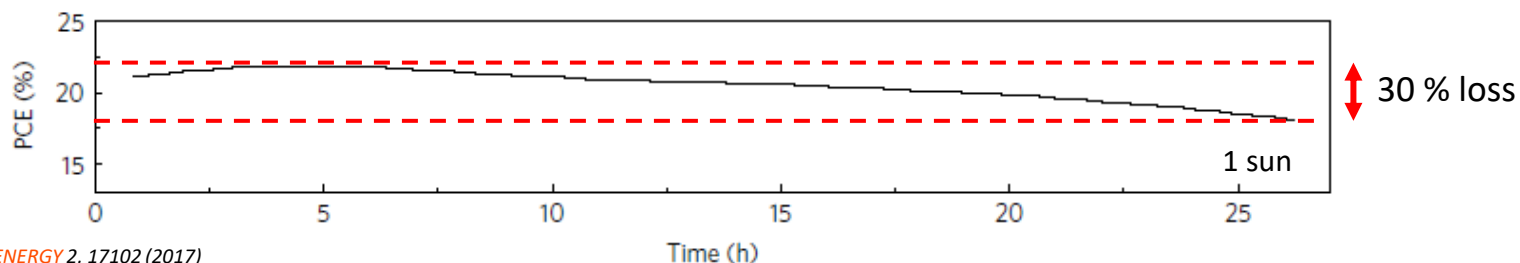
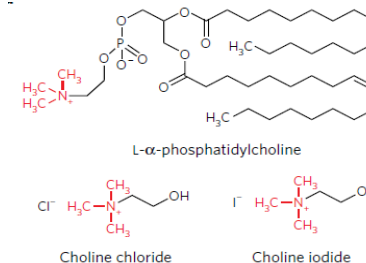


Deep defect passivation
anionic Pb-I and cationic Pb clusters

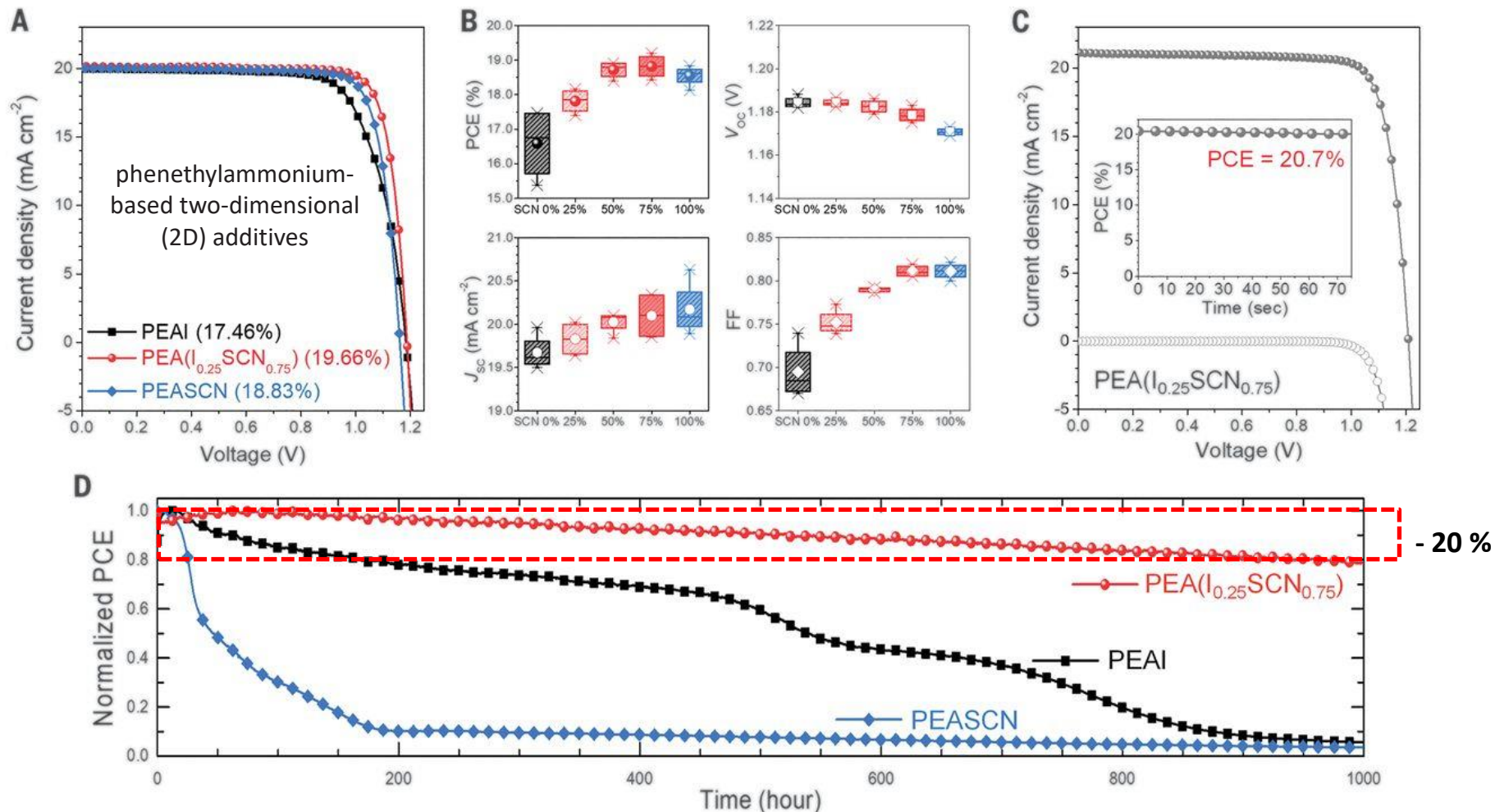
Non-radiative recombination:
Voltage Increase
Efficiency Increase



positive charged ammonium group ($-N(CH_3)_3^+$)
negative charged phosphate ($-PO_4^-$)



Efficient, stable silicon tandem cells enabled by anion-engineered wide-bandgap perovskites



ISOS Protocols for PSCs

nature
energy

CONSENSUS STATEMENT

<https://doi.org/10.1038/s41560-019-0529-5>

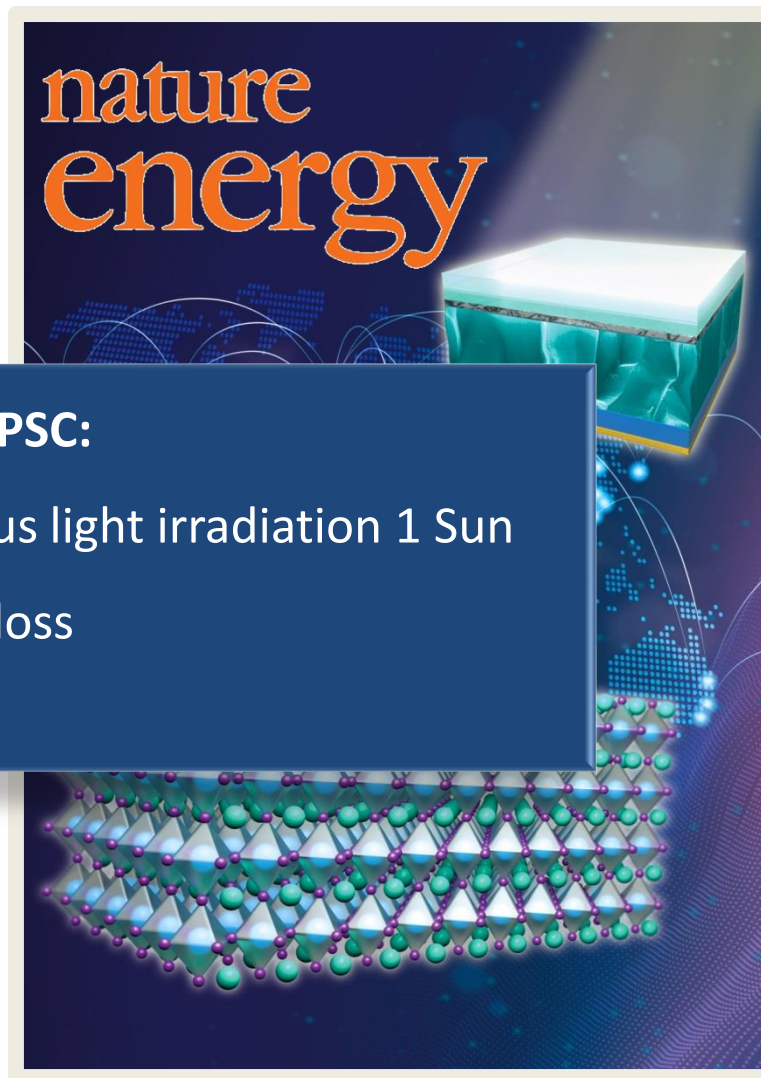
OPEN

Consensus statement for stability assessment and reporting for perovskite photovoltaics based on ISOS procedures

Mark V. Khenkin^{1,2}, Eugene A. Katz^{1,2}, Christoph Brabec^{7,8}, Francesca Brunetti^{1,2}, Rongrong Cheacharoen¹², Yi-Bing Cheng^{1,2}, Konrad Domanski¹⁶, Michał Dusza¹⁶, Yulia Galagan²², Diego Di Girolamo^{1,2}, Harald Hoppe²⁷, Jeff Kettle²⁸, Hans Korte^{1,2}, Yueh-Lin Loo^{11,33}, Joseph M. Luther^{1,2}, Muriel Matheron¹⁵, Michael McGehee^{1,2}, Ana Flavia Nogueira³⁸, Çağla Odabasi^{1,2}, Francesca De Rossi^{9,41}, Michael Saliba^{1,2}, Samuel D. Stranks⁴⁶, Wolfgang Tress²⁵, Pavel A. Troshin^{47,48}, Vida Turkovic³⁵, Sjoerd Veenstra²², Iris Visoly-Fisher^{1,3}, Aron Walsh^{49,50}, Trystan Watson⁴¹, Haibing Xie⁵¹, Ramazan Yildirim³⁹, Shaik Mohammed Zakeeruddin²⁴, Kai Zhu⁶ and Monica Lira-Cantu^{51*}

Stable PSC:

- > 1000 h under continuous light irradiation 1 Sun
- Less than 10% Efficiency loss



Shallow Iodine Defects Accelerate the Degradation

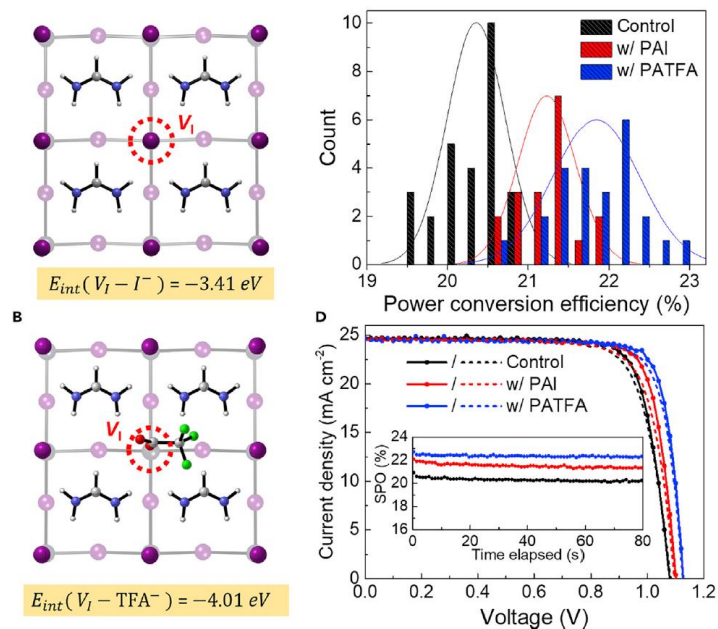
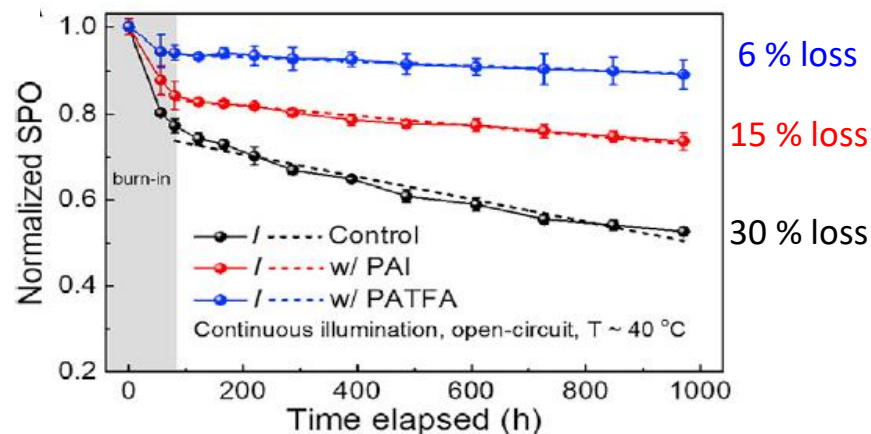
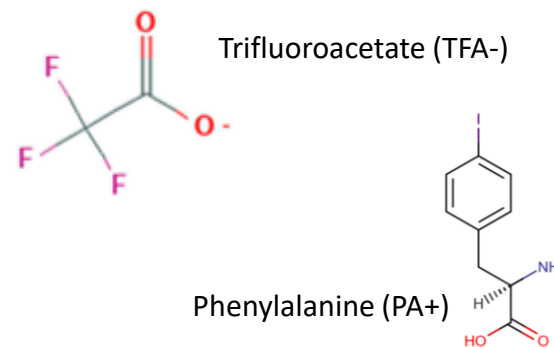


Table 1. Distribution of the Device Photovoltaic Parameters

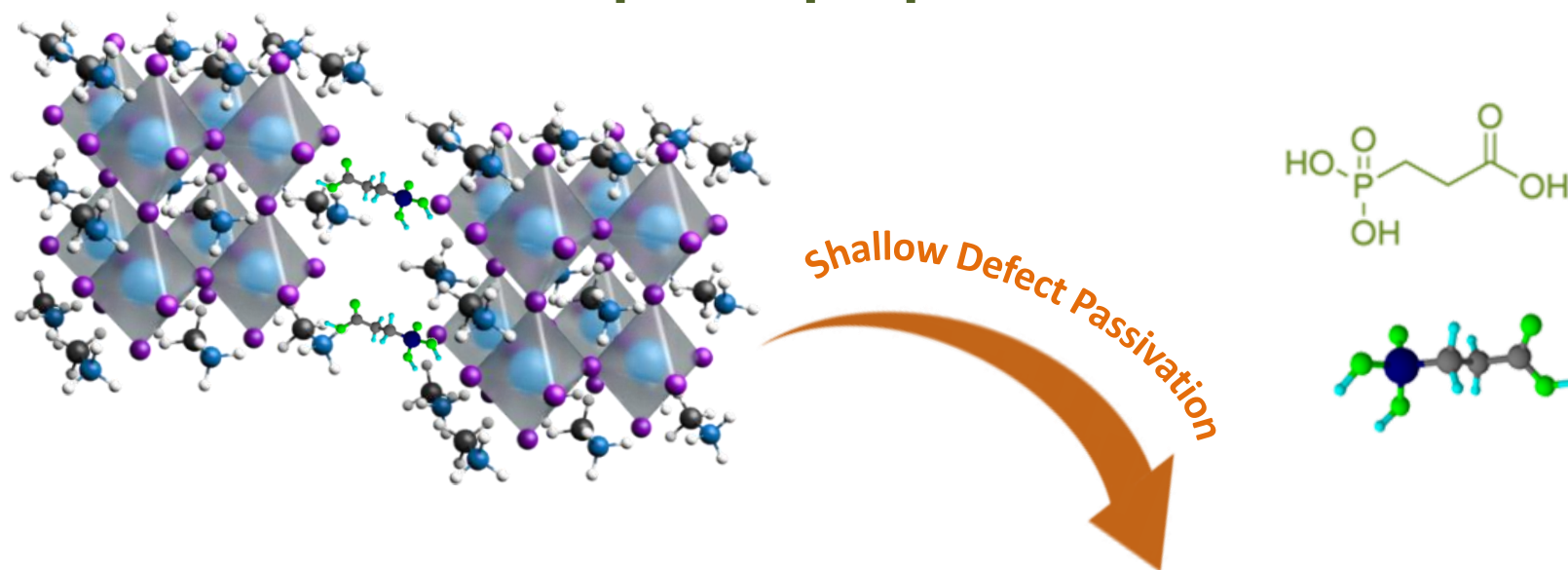
	V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF	PCE (%)	SPO (%)
Control	1.073 ± 0.012 (1.079)	24.45 ± 0.12 (24.67)	0.774 ± 0.012 (0.787)	20.32 ± 0.35 (20.95)	20.3
w/PAI	1.103 ± 0.009 (1.101)	24.49 ± 0.13 (24.62)	0.786 ± 0.014 (0.806)	21.23 ± 0.36 (21.86)	21.4
w/ PATFA	1.120 ± 0.013 (1.127)	24.51 ± 0.10 (24.61)	0.796 ± 0.019 (0.829)	21.84 ± 0.35 (22.98)	22.4

Average photovoltaic parameters of the control and treated devices. Parenthesis indicate parameters measured from champion devices for each condition. Abbreviations are V_{oc} , open-circuit voltage; J_{sc} , short-circuit current density; FF, fill factor; PCE, power conversion efficiency; SPO, stabilized power output.

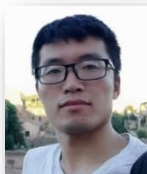
Replacement of I with an alternative anion



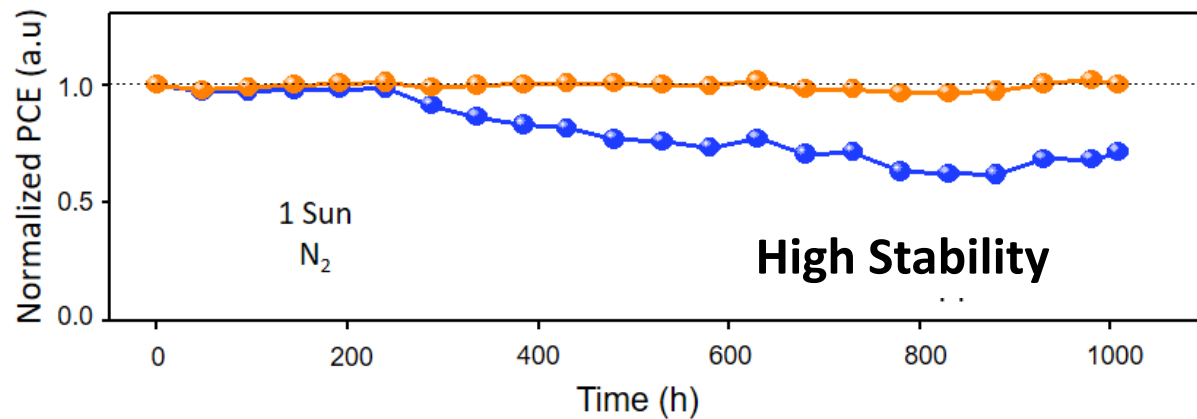
3-Phosphonopropionic Acid



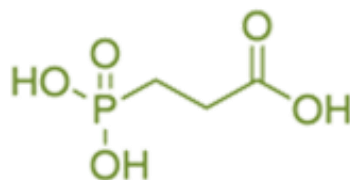
Haibing Xia



Zaiwei Wang



Additive Selection: Why phosphonate/Carboxillate



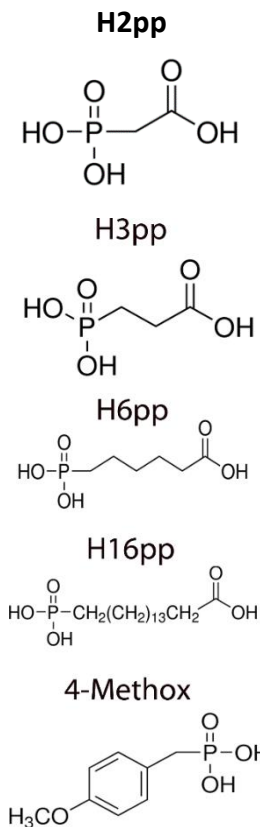
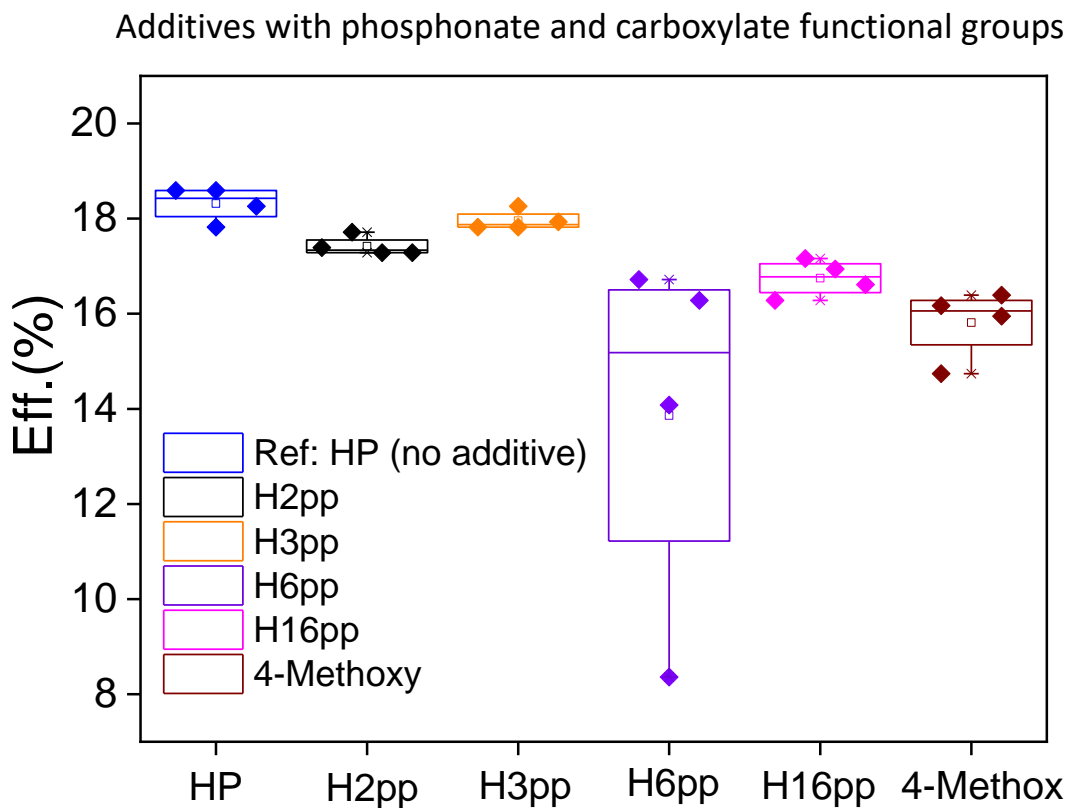
3-Phosphonopropionic Acid

-PO(OH)₂ and -COOH anchoring agents in DSSCs:

- PO(OH)₂ was employed to increase the surface binding stability**
- Carboxylic acids were employed to increase the electron injection efficiency.**

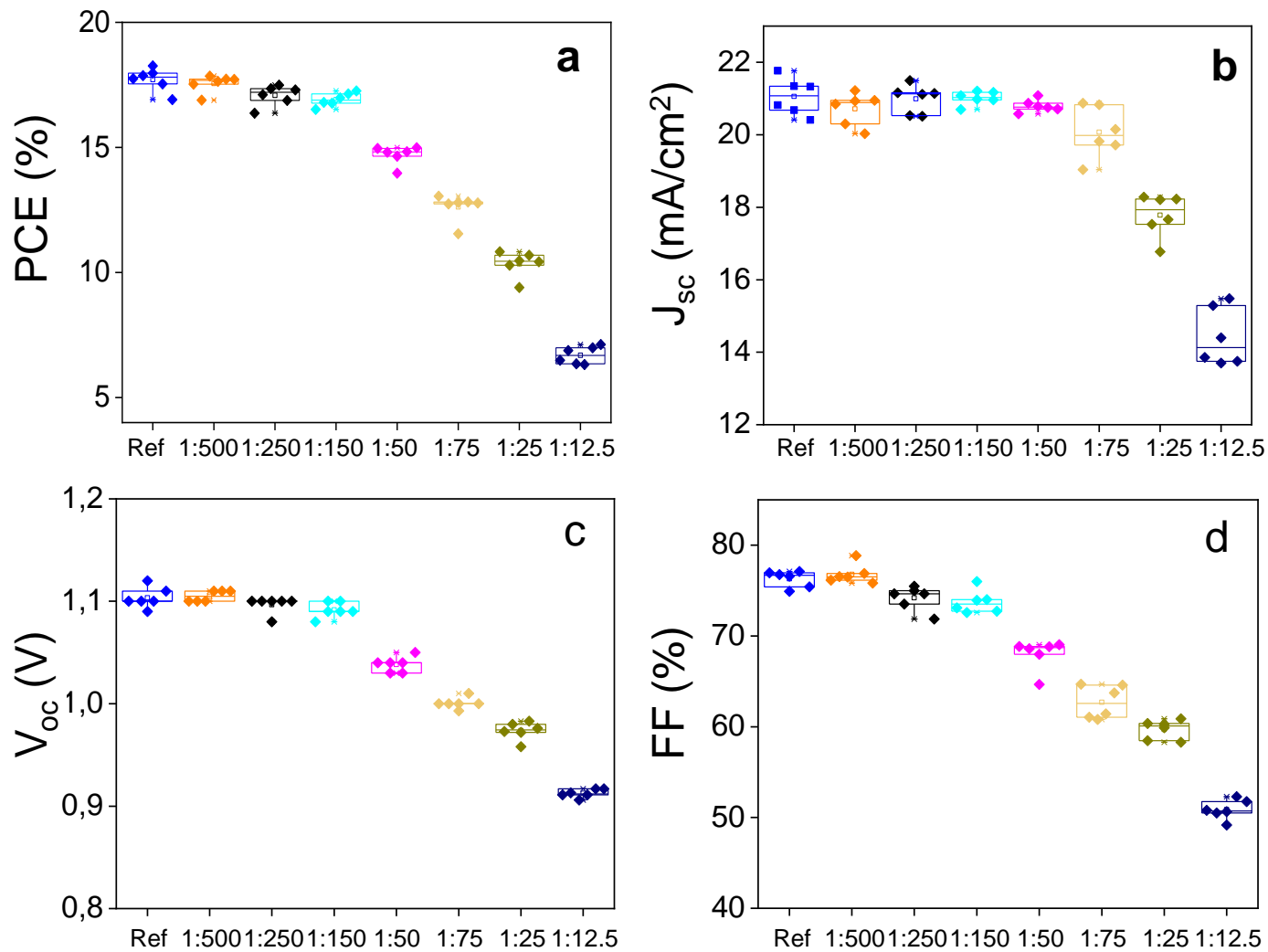
**Bonding through the phosphonic acid group → more stable than carboxylic or amine groups
but ...charge injection rates can be affected
(by the tetrahedral phosphorous center and loss of conjugation)**

Effect of type of molecule



Increasing chain length

Effect of molecule H3pp concentration

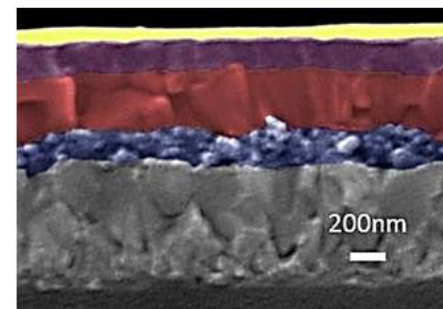
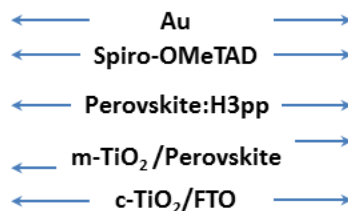
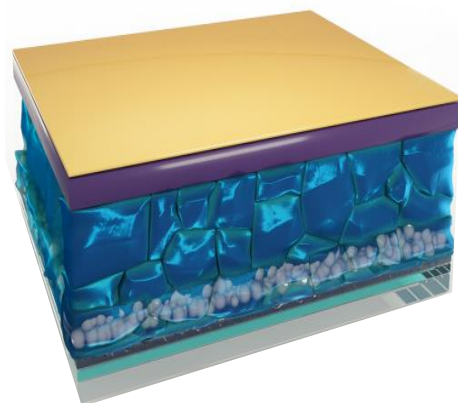


HP:H3pp ratio

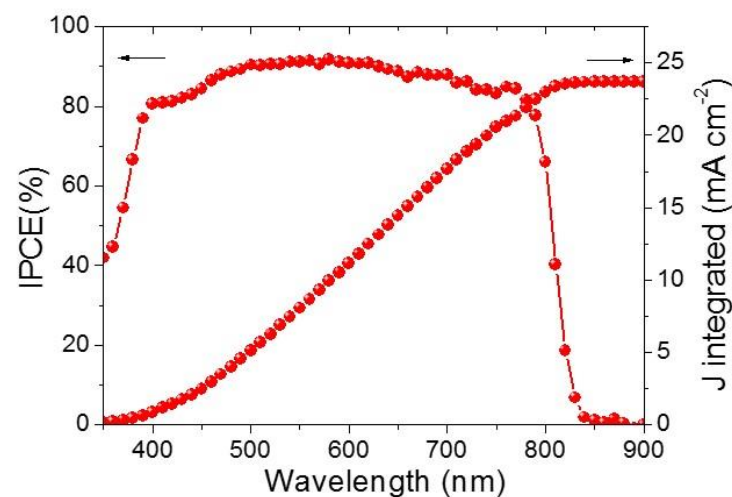
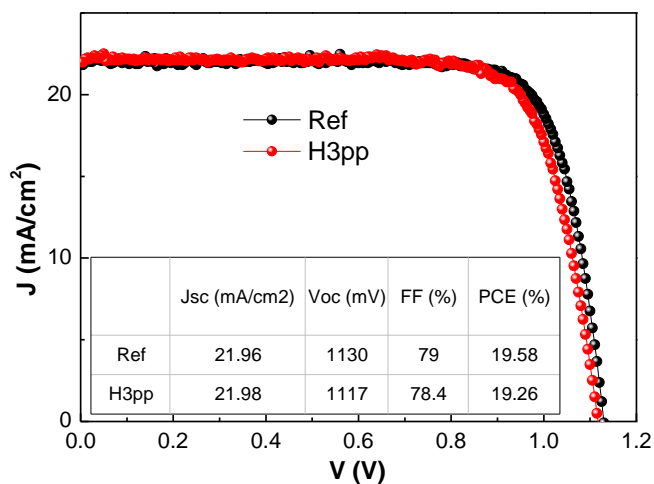
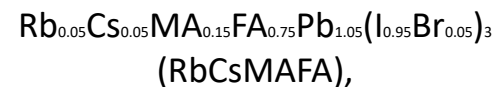
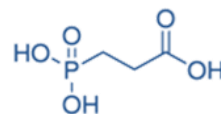
Champion Solar Cell: 21.1 % eff



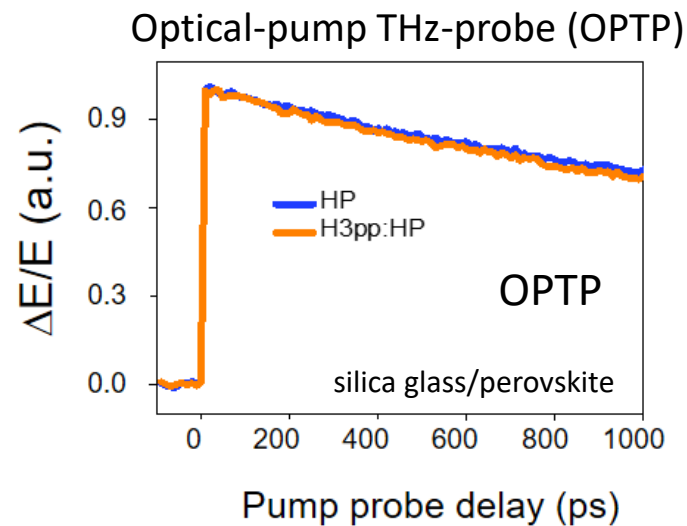
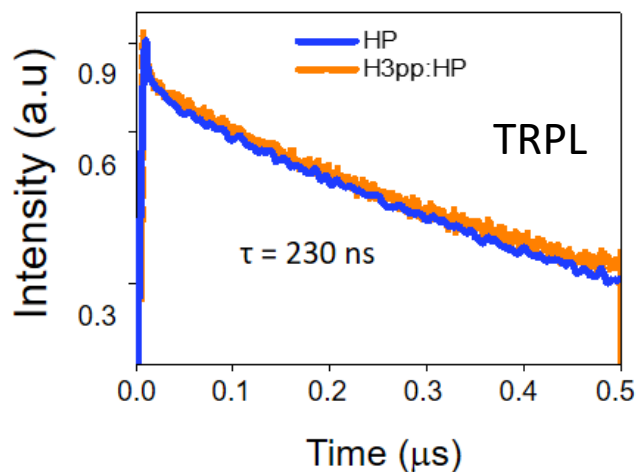
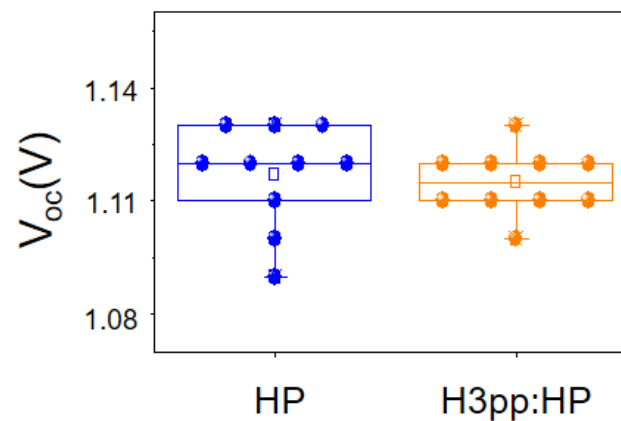
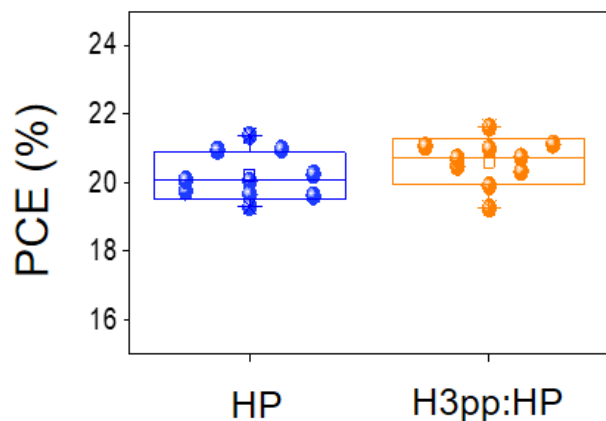
Haibing Xia



3-Phosphonopropionic Acid



Recombination behaviour



Charge carrier life time (non-radiative recombination)

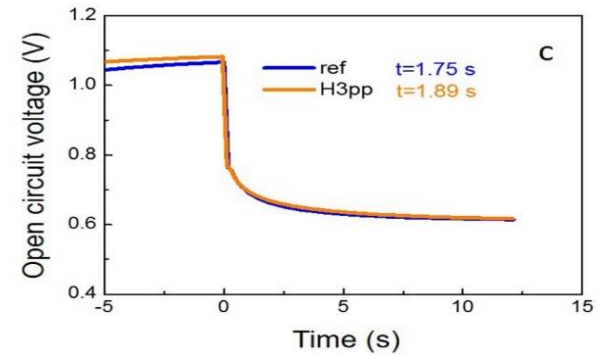
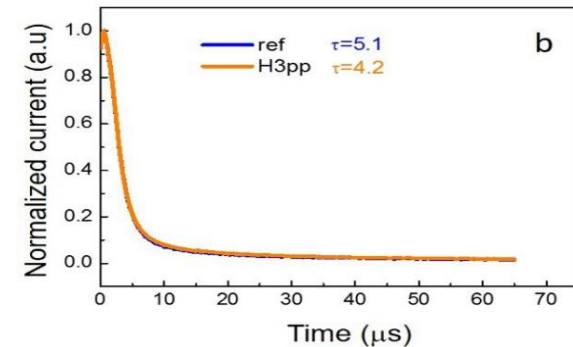
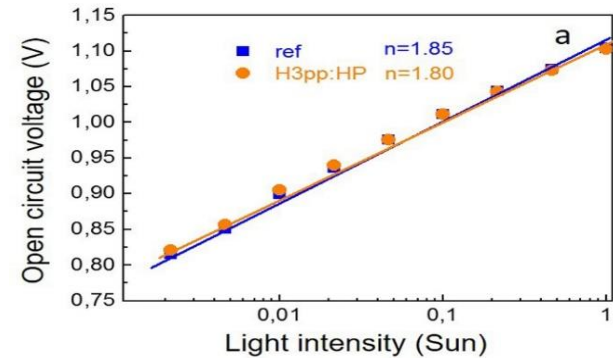
Light-induced mobile charges

Effect of additive

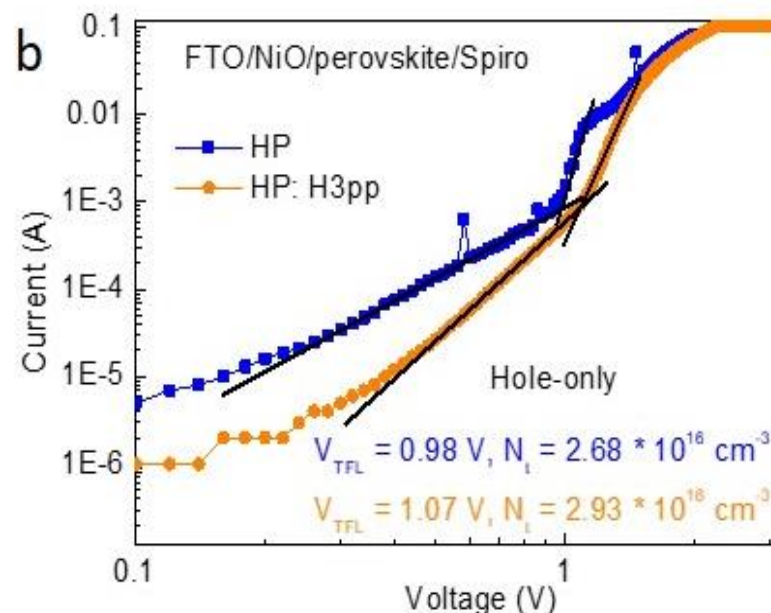
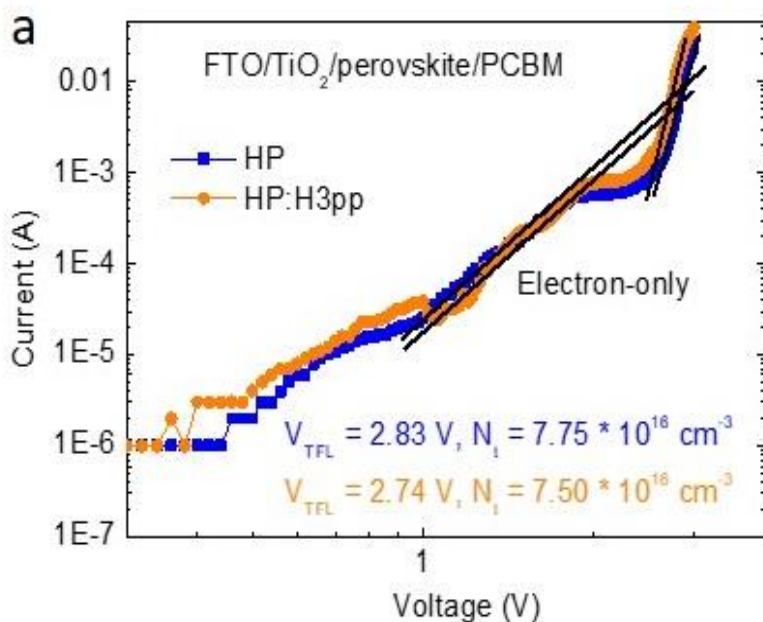
- (a) Light intensity dependent V_{oc}
- (b) Transient photocurrent
- (c) Open circuit voltage decay.

- Ideality factors with $n_{id} = 1.80$ and 1.85
- Very similar p-n junction quality and trap-assisted recombination
- Similar carrier transport and recombination properties

FTO/c-TiO₂/m-TiO₂/HP/spiro-OMeTAD/Au



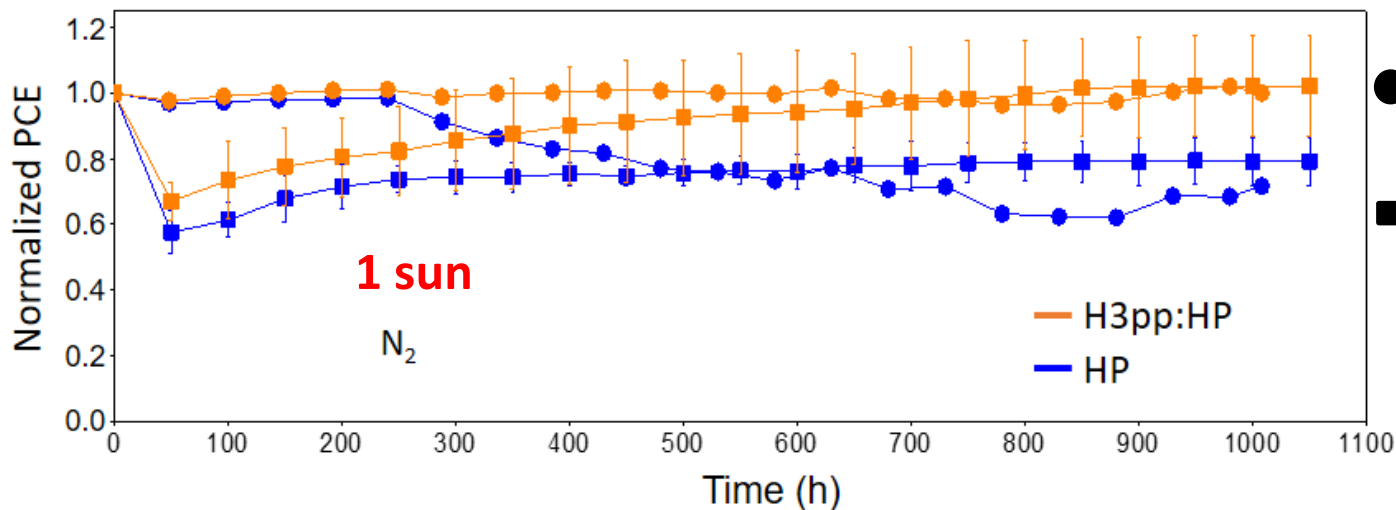
Effect of additive: Trap density



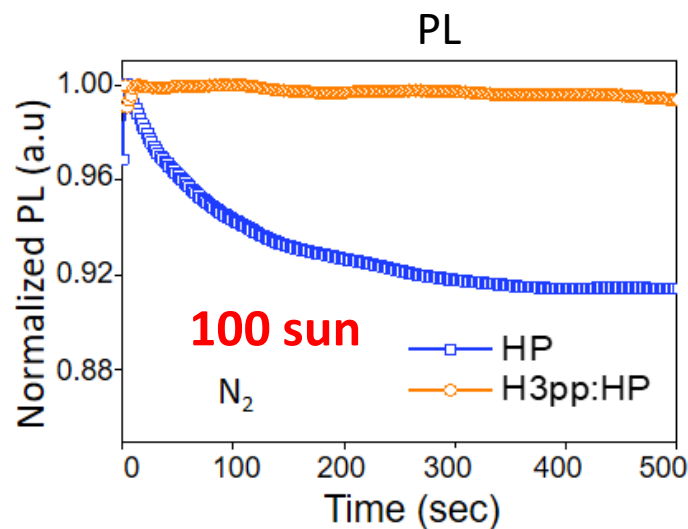
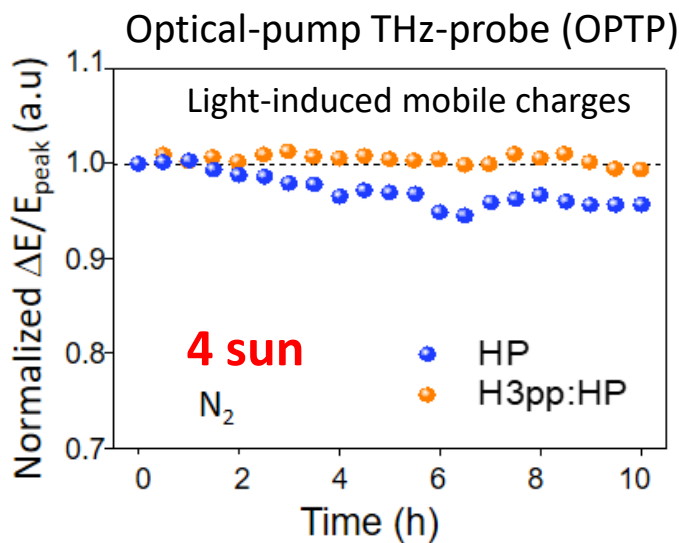
Space-charge-limited current (SCLC) for electron-only (a) and hole-only (b) devices with and without the addition of the H3pp additive.

→ Passivation of deep defects is negligible.

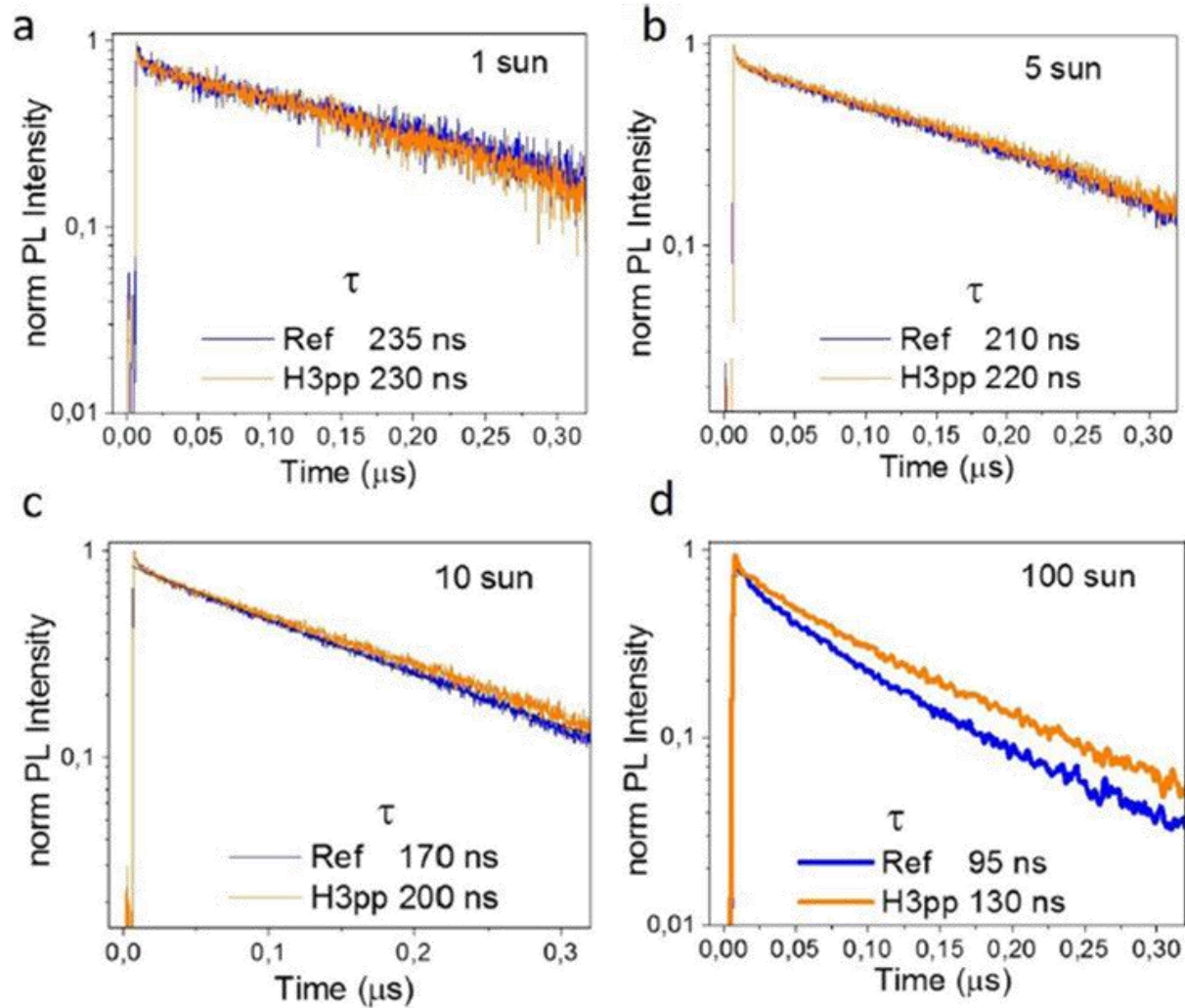
Operational stability



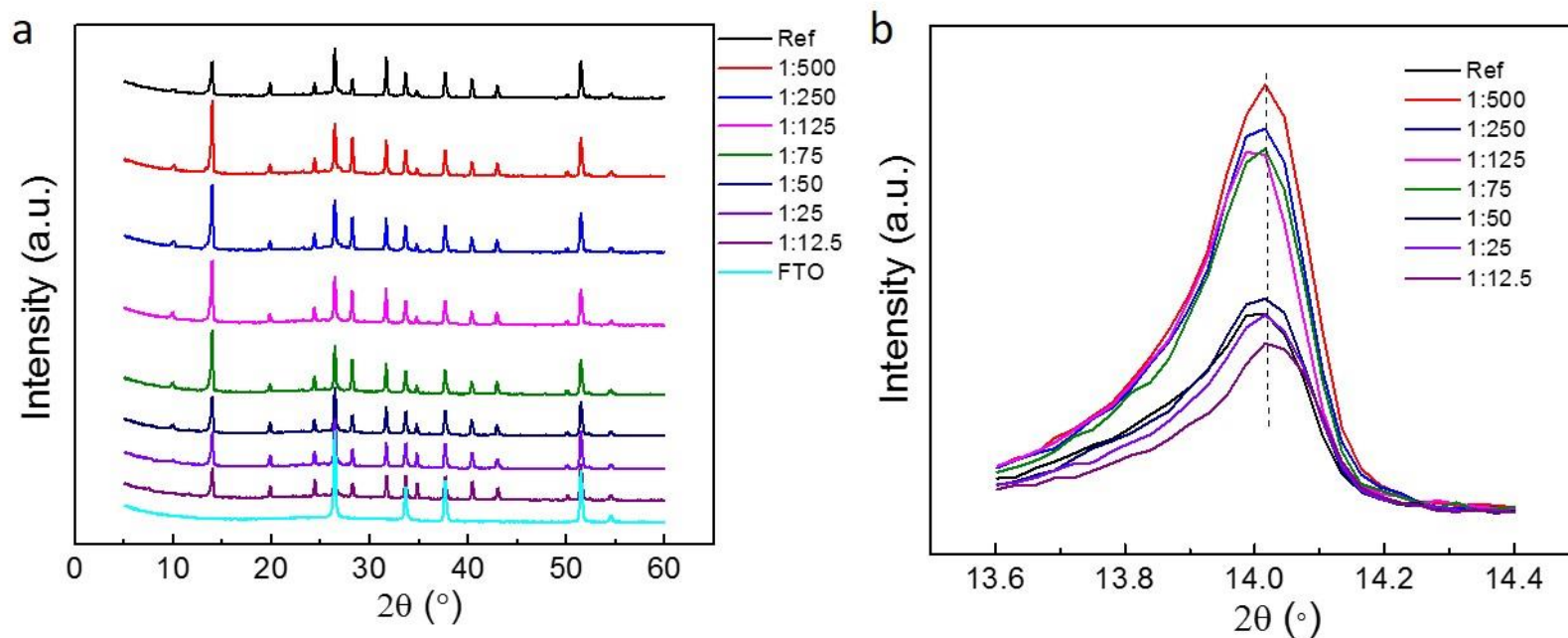
- Rb_{0.05}Cs_{0.05}MA_{0.15}FA_{0.75}Pb_{1.05}(I_{0.95}Br_{0.05})₃ (RbCsMAFA),
- Cs_{0.05}MA_{0.15}FA_{0.80}Pb_{1.05}(I_{0.85}Br_{0.15})₃ (CsMAFA)



TRPL at different light intensity (fluences)



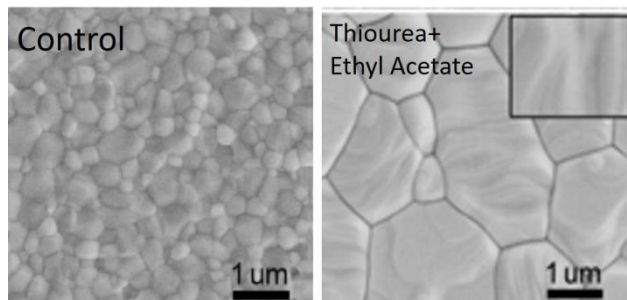
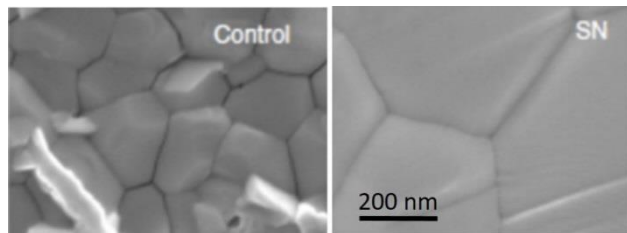
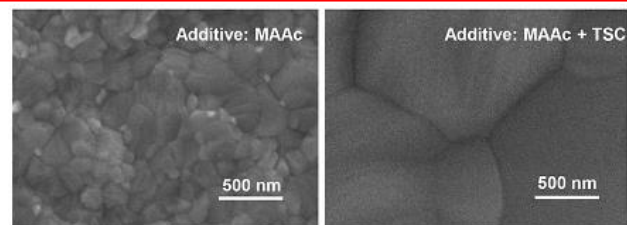
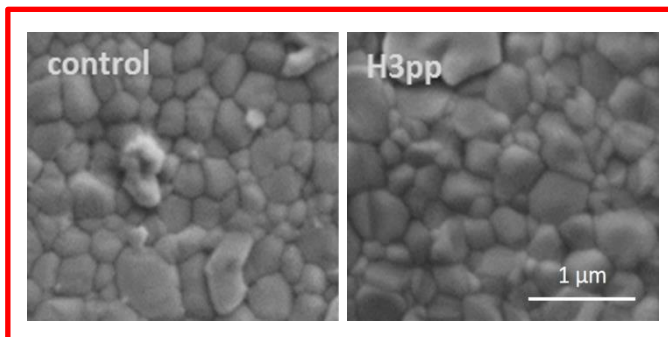
No incorporation of the additive into the structure



RbCsMAFA

The full width at half maximum (FWHM) of the main perovskite peak (-111), $2\theta = 14^\circ$, is 0.147 for both of the reference and H3pp-doped (1:500) samples, reflecting that **the average grain size is not affected by H3pp**.

No new peaks and peak shifts are observed, implying that **the H3pp not likely incorporates into the perovskite crystal lattice**, in agreement with the solid-state NMR results.

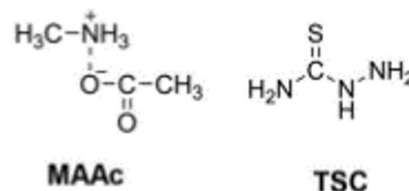


Grain Size

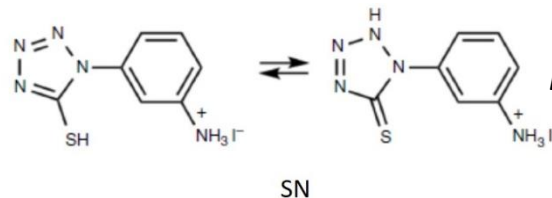
H3PP

This Work

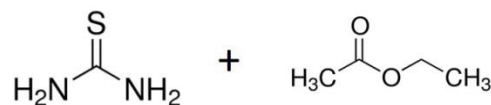
Haibing, X. Submitted



Grancini, et al. Nat. Commun. 8, 15684 (2017).



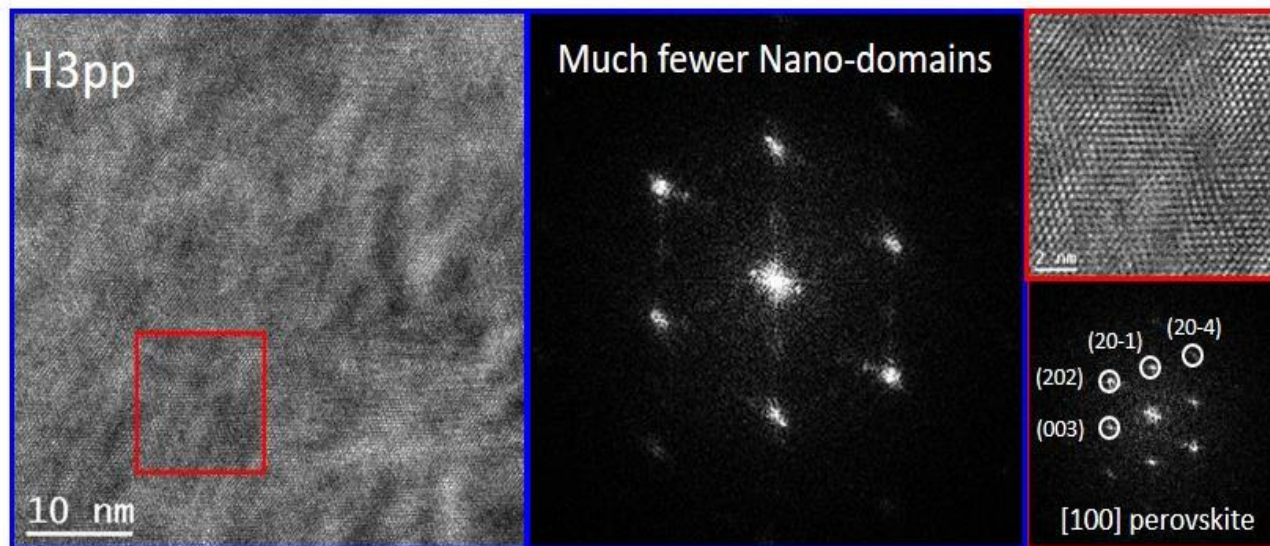
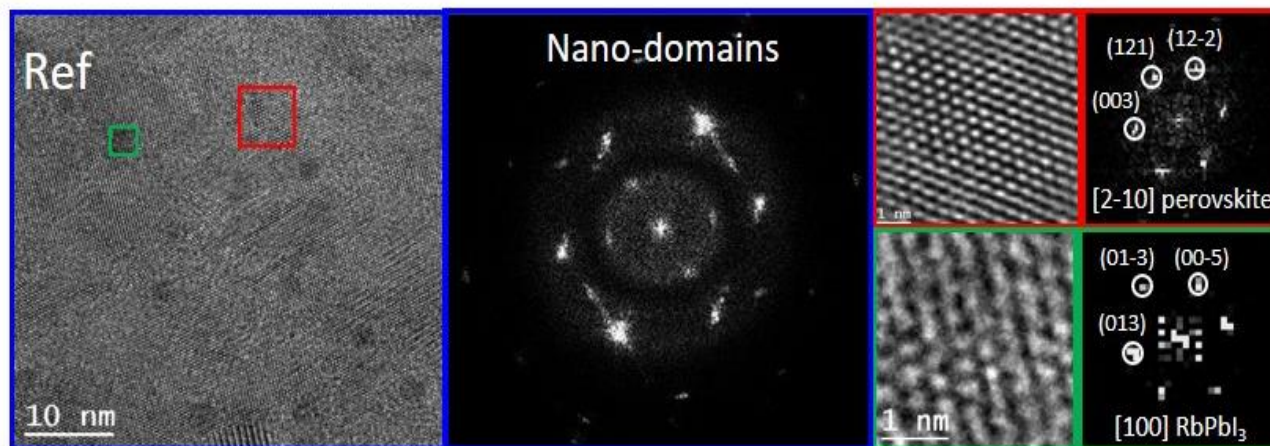
Bi, D. et al. Nat. Commun. 9, 4482 (2018).



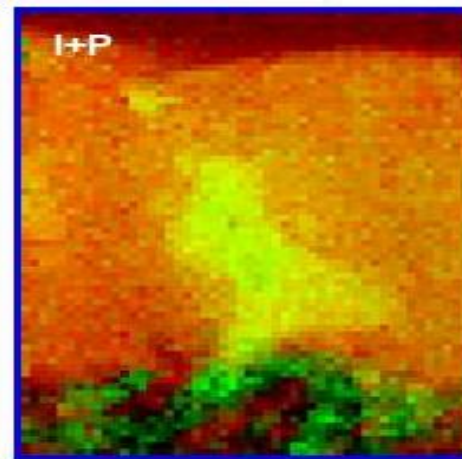
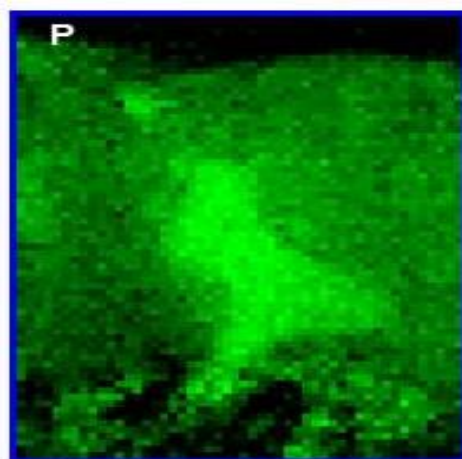
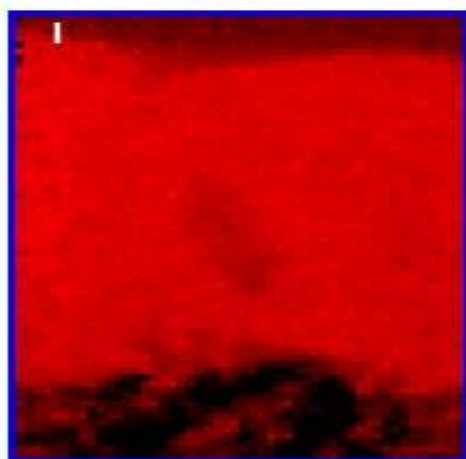
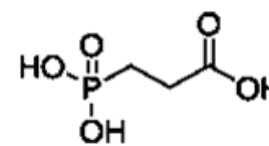
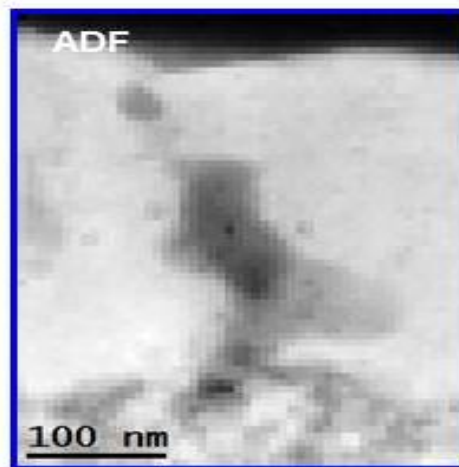
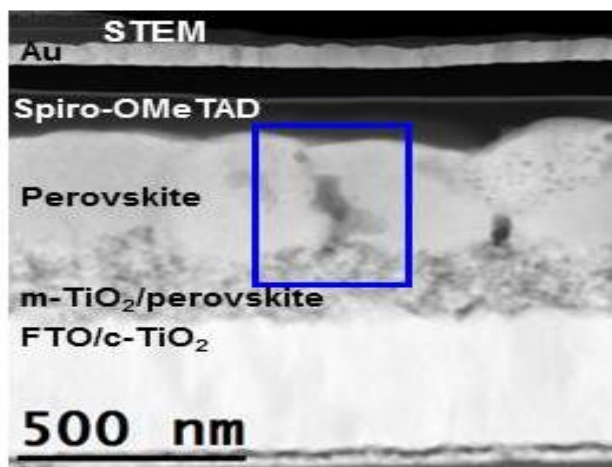
Fei, C. et al. Adv. Energy Mater. 7, 1602017 (2017).

TEM

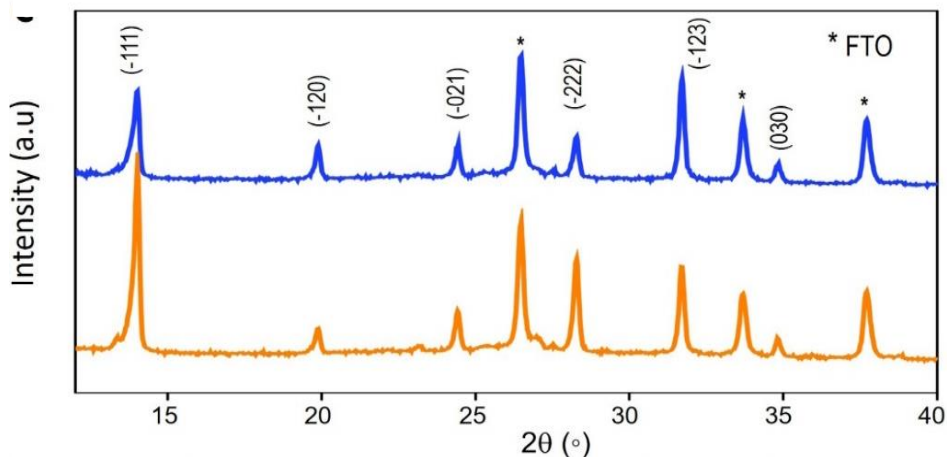
Highly homogeneous films



Electron energy loss spectroscopy (EELS) chemical composition maps



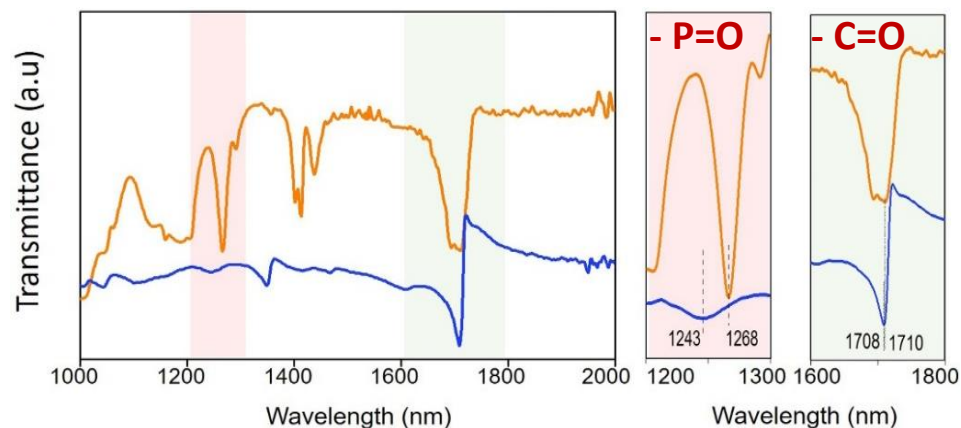
Homogeneous distribution



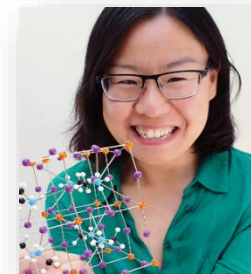
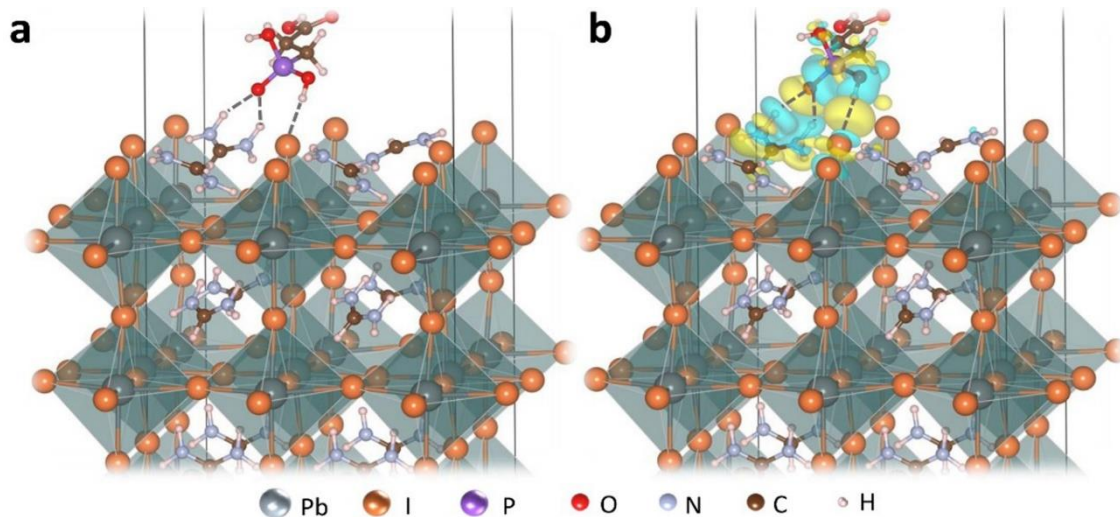
Interaction additive/HP

P=O stretching: 1,220 - 1,300 nm
 C=O stretching: 1,600 - 1,800 nm.

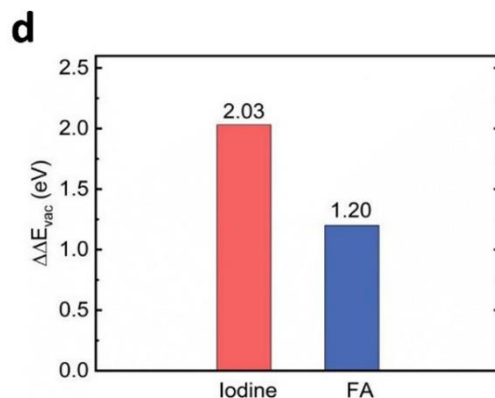
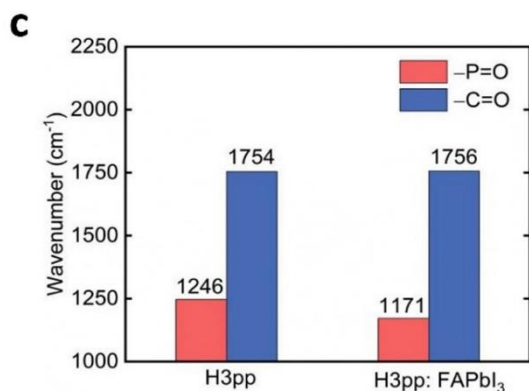
- P=O at $1268\text{ cm}^{-1} \rightarrow$ to 1243 cm^{-1}
- C=O unchanged



DFT Calculations



Shuxia Tao

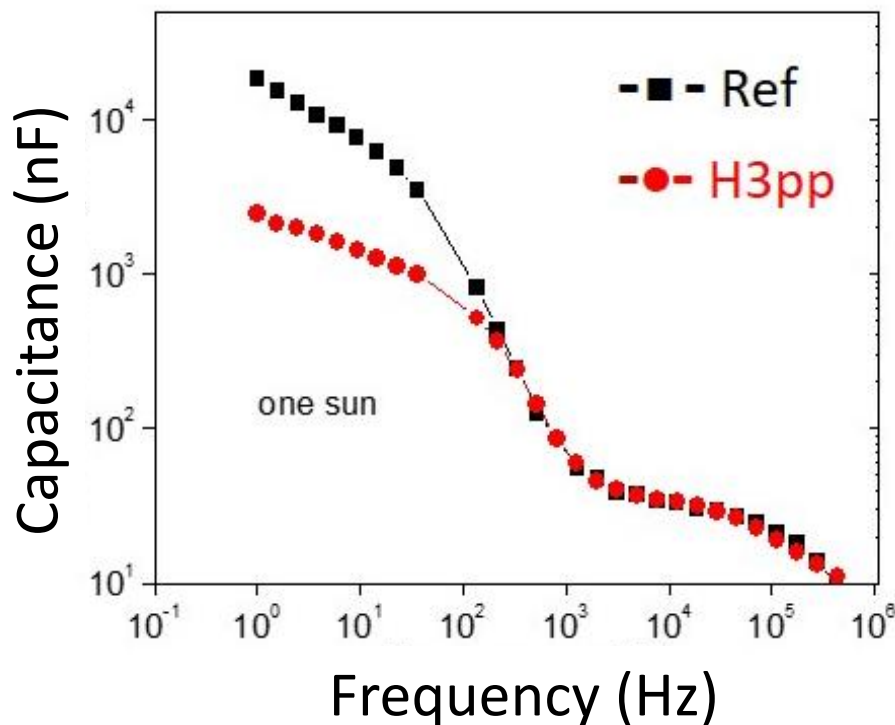


The H3pp additive strongly bonds to the perovskite through the $-PO(OH)_2$ functional group via two types of hydrogen bonds ($H\cdots I$ and $O\cdots H$), passivating shallow point defects (e.g., FA and I vacancies).

Good correlation with the FTIR data

ION MIGRATION: IMPEDANCE SPECTROSCOPY

Frequency (f) dependent capacitance (C)



From Nyquist Plot of impedance spectra (IS)

$$C = 1/(2\pi f Z'')$$

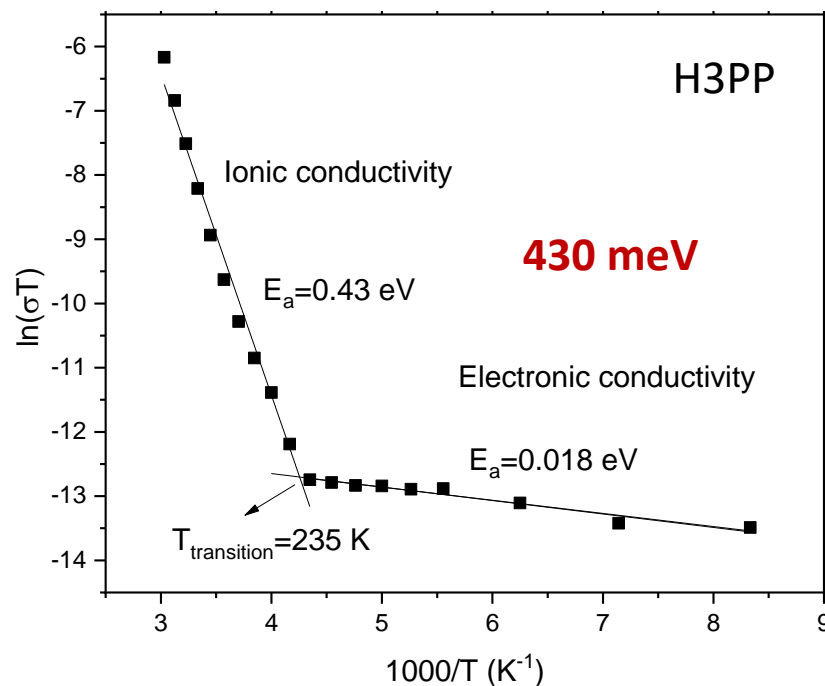
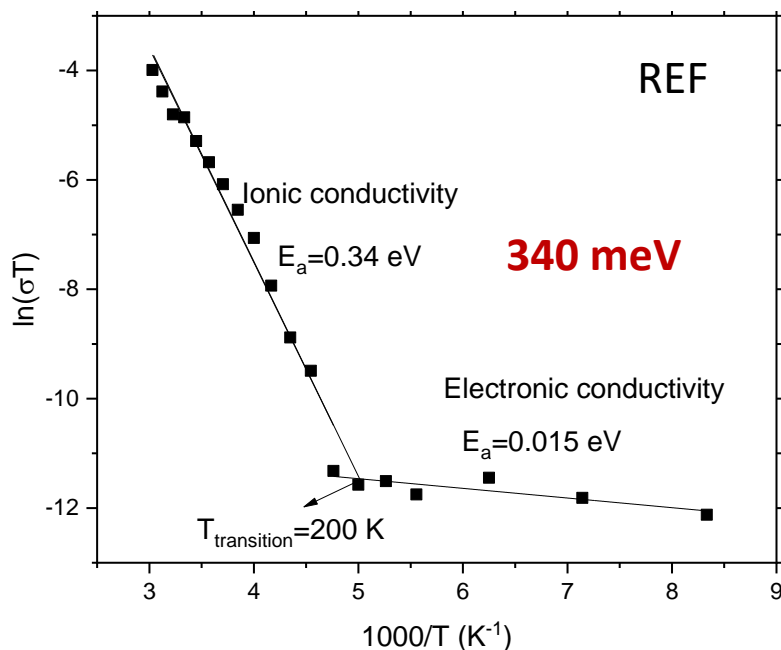
f is frequency in Hz

Z'' is the imaginary part

The capacitance in the low frequency range (1-100 Hz) is one order of magnitude lower in the H3pp doped device, indicating an **effective reduction in ion migration and charge accumulation** at the interfaces.

ION MIGRATION: ACTIVATION ENERGY

Temperature dependent conductivity (Dark)



higher activation energy than Ref sample → indicating the ion migration is mitigated.

Deep Defect Vs Shallow Defect passivation

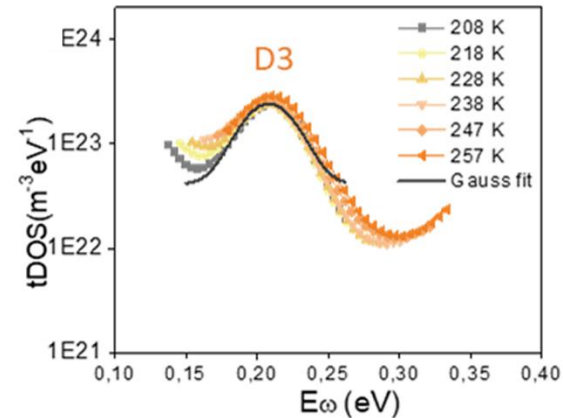
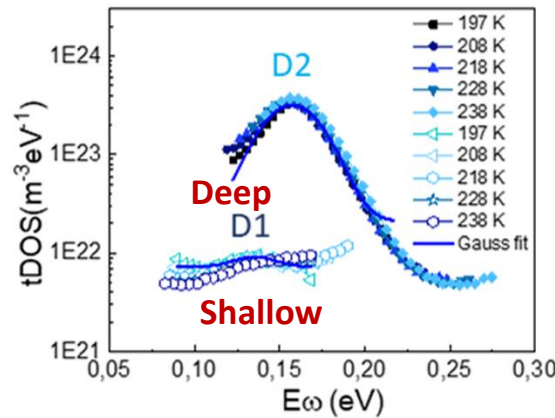
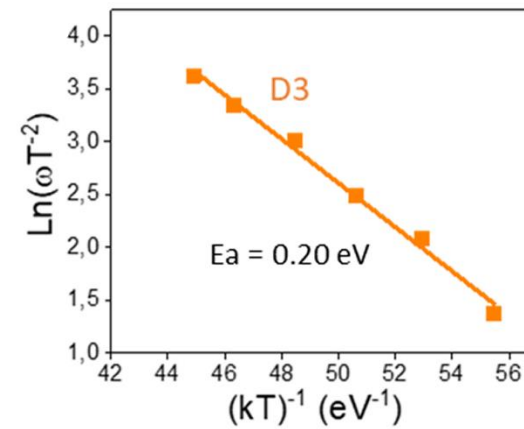
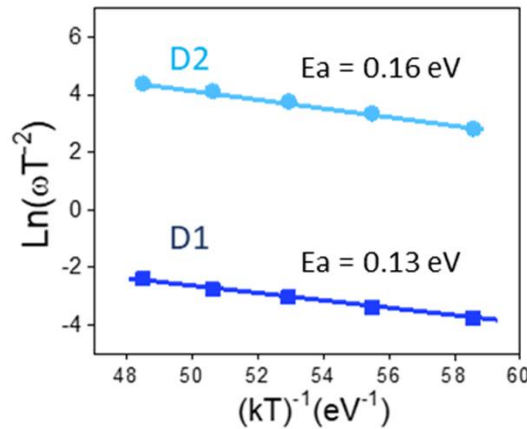
Thermal admittance spectroscopy

No Additive

Additive



Feng Gao
(Linköping University)



Deep Defect Vs Shallow Defect passivation

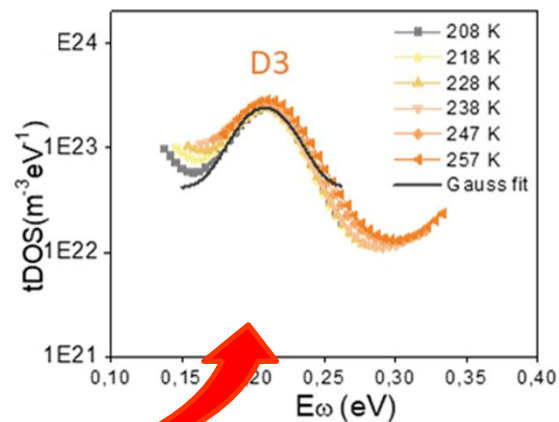
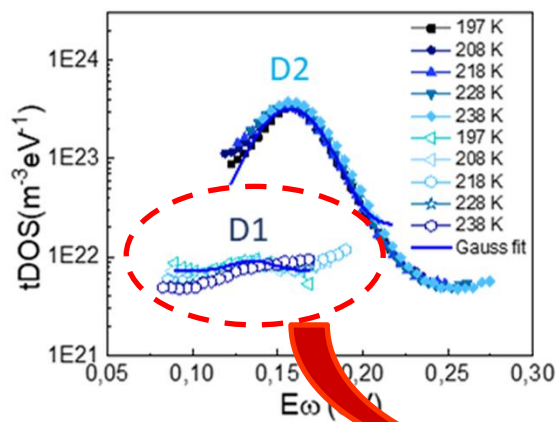
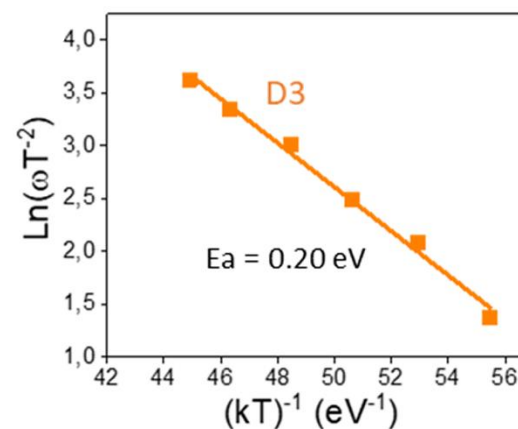
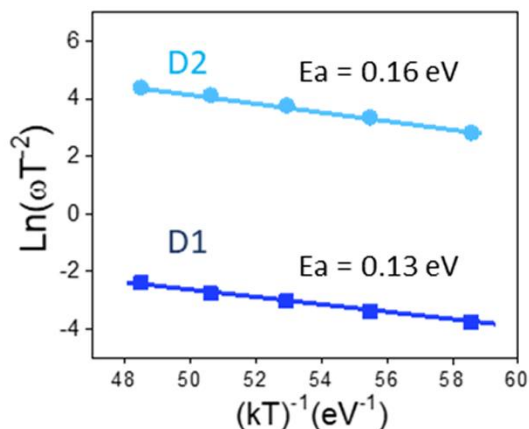
Thermal admittance spectroscopy

No Additive

Additive

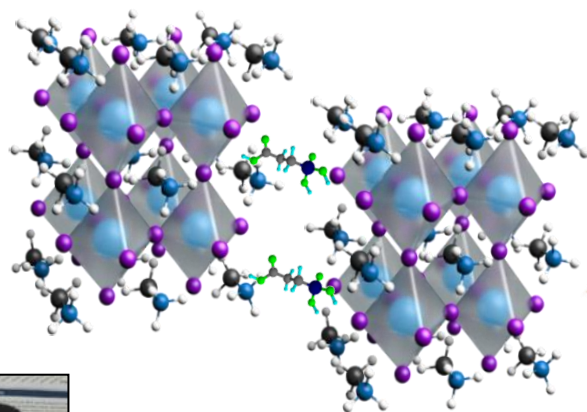


Feng Gao
(Linköping University)

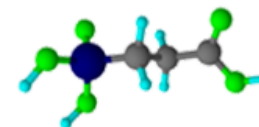
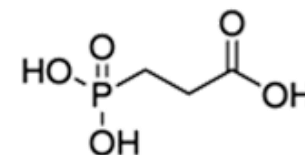


SHALLOW

Deep defect passivation → Efficiency
 Shallow defect passivation → Stability



Shallow Defect Passivation



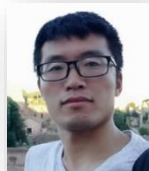
3-Phosphonopropionic Acid



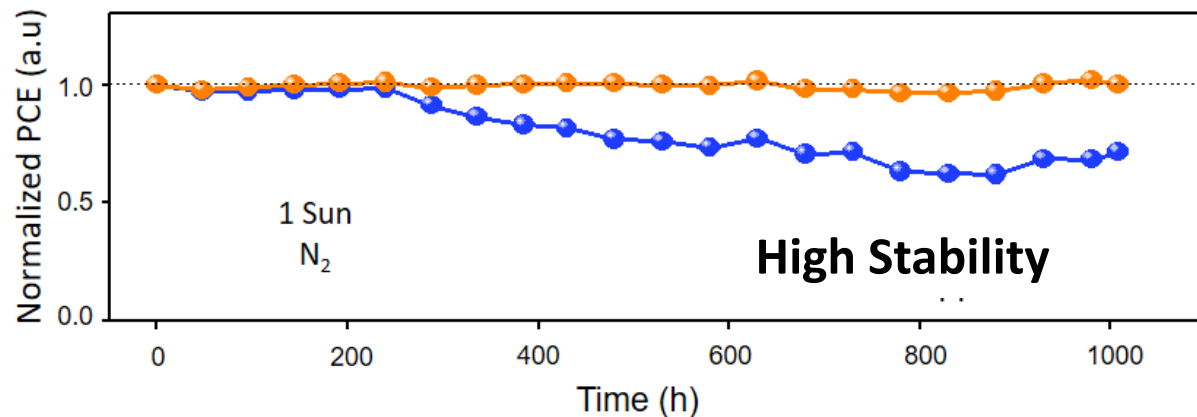
Carlos Pereyra



Haibing Xia



Zaiwei Wang



Conclusions

Passivation of both shallow and deep defects is needed!

The current understanding of point defects in PSCs indicates that passivation of deep defects (e.g., Pb-I antisite defects) reduces the nonradiative losses and has a direct impact on the device performance (V_{oc} and efficiency).

In our work, the PLQE and OTP results at low fluences (~ 1 sun) rule out any variation in the non-radiative defect concentration. However, analyses at increasing fluences (above 10 suns) indicate a small decrease in the deep trap density, which has an enormous impact on the device stability but not on the device performance.

The H3pp additive strongly bonds to the perovskite through the $-PO(OH)_2$ functional group via two types of hydrogen bonds ($H\cdots I$ and $O\cdots H$), passivating shallow point defects (e.g., FA and I vacancies).

Other intrinsic factors could be influencing stability: concentration, size and structure of the additive.

Acknowledgements

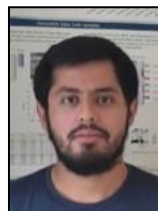
Haibing Xie, Carlos Pereyra, Pengyi Tang, **Jordi Arbiol**, Monica Lira-Cantu
Daniel Prochowicz, Shaik Mohammed Zakeeruddin, **Michael Grätzel**
Zaiwei Wang, Anand Agarwalla, Hui-Seon Kim, **Anders Hagfeldt**
Krzysztof Gałkowski, **Miguel Anaya**, **Samuel D. Stranks**
Zehua Chen, Mike Pols, **Shuxia Tao**
Klaas-Jan Tielrooij, Mischa Bonn, Shuai Fu, Xiaoyu Jia
Dominik Józef Kubicki
Xavier Borrís Lyndon Emsley
Hai I. Wang

TAS analysis:

Feng Gao, Fan Fu
Chunxiong Bao
Xiaoxiao Sun



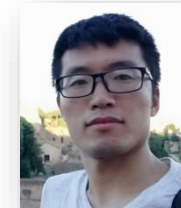
Anders Hagfeldt



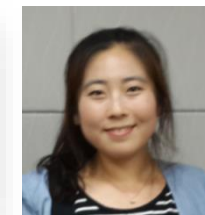
Carlos Pereyra



Haibing Xia



Zaiwei Wang



Hui-Seon Kim



Jose Caicedo



Marc Maymo



Gustavo Ceballos



Jose Santiso

Acknowledgements

To the Nanostructured Materials for
Photovoltaic Energy Group



Dr. Sonia Raga



Dr. Masoud
Karimipour



Dr. Fatemeh
Ansari



Dr. Carlos
Pereyra



Kenedy Tabah



Fanny Bauman



Ashitha P.P.



Marcel Zambrzycki



Eudald Vehi



Pol Lorenzo



Pierre-Antoine
Zemmouche



Jose Caicedo



Marc Maymo

COMING SOON

APL Energy

Bridging basic energy research and innovative technology that will impact the future



Editor-in-Chief:

Prof. Mónica Lira-Cantú

Catalan Institute of Nanoscience and Nanotechnology (ICN2)

Topics Include:

- Energy Storage
- Energy Harvesting
- Energy Generation
- Materials in Energy
- Energy Applications
- Renewable Energy



Follow us on Twitter
@aplenergy



Learn more at
publishing.org/apl-energy



VIPERLAB: EU project aims to boost perovskite solar industry in Europe



Thank you for your attention!

Prof. Monica Lira-Cantu
monica.lira@icn2.cat